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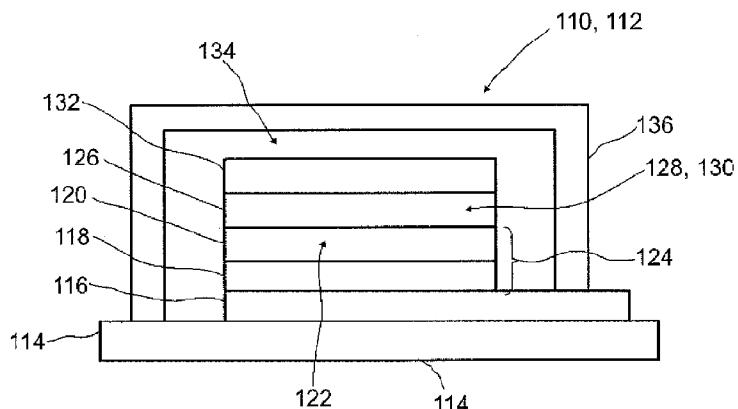
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(54) Titel: PHOTOVOLTAIC ELEMENT

(54) Bezeichnung : PHOTOVOLTAISCHES ELEMENT

FIG.1



(57) Abstract: A photovoltaic element (110) is proposed for conversion of electromagnetic radiation to electrical energy, more particularly a dye solar cell (112). The photovoltaic element (110) has at least one first electrode (116), at least one n-semiconductive metal oxide (120), at least one electromagnetic radiation-absorbing dye (122), at least one solid organic p-semiconductor (124) and at least one second electrode (132). The p-semiconductor (124) comprises silver in oxidized form.

(57) Zusammenfassung:

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WO 2012/104742 A1



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MD, RU, TJ, TM), europäisches (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG). — *vor Ablauf der für Änderungen der Ansprüche geltenden Frist; Veröffentlichung wird wiederholt, falls Änderungen eingehen (Regel 48 Absatz 2 Buchstabe h)*

Es wird ein photovoltaisches Element (110) zur Umwandlung elektromagnetischer Strahlung in elektrische Energie vorgeschlagen, insbesondere eine Farbstoffsolarzelle (112). Das photovoltaische Element (110) weist mindestens eine erste Elektrode (116), mindestens ein n-häibleitendes Metalloxid (120), mindestens einen eine elektromagnetische Strahlung absorbierenden Farbstoff (122), mindestens einen festen organischen p-Halbleiter (126) und mindestens eine zweite Elektrode (132) auf. Der p-Halbleiter (126) weist Silber in oxidiertter Form auf.

Photovoltaic element

5 Description

Field of the invention

10 The invention relates to a photovoltaic element, to a process for production of a solid organic p-semiconductor for use in an organic component, and to a process for production of a photovoltaic element. Such photovoltaic elements and processes are used to convert electromagnetic radiation, especially sunlight, to electrical energy. More particularly, the invention can be applied to dye solar cells.

15 State of the art

20 The direct conversion of solar energy to electrical energy in solar cells is based generally on what is called the "internal photo effect" of a semiconductor material, i.e. the production of electron-hole pairs by absorption of photons and the separation of the negative and positive charge carriers at a p-n junction or a Schottky contact. In this way, a photovoltage is generated, which, in an external circuit, can cause a photocurrent through which the solar cell releases its power. The semiconductor can generally only absorb those photons which have an energy greater than the bandgap thereof. The size of the semiconductor bandgap thus generally determines the proportion of sunlight which 25 can be converted to electrical energy.

30 Solar cells based on crystalline silicon were produced as early as the 1950s. The technology at that time was supported by use in space satellites. Even though silicon-based solar cells now dominate the market on Earth, this technology still remains costly. Attempts are therefore being made to develop new approaches which are less expensive. Some of these approaches will be outlined hereinafter, which constitute the basis of the present invention.

35 An important approach to the development of new solar cells is that of organic solar cells, i.e. solar cells which comprise at least one organic semiconductor material, or solar cells which, instead of solid inorganic semiconductors, comprise other materials, especially organic dyes or even liquid electrolytes and semiconductors. A special case among the innovative solar cells is that of dye solar cells. The dye solar cell (DSC) is one of the most efficient alternative solar cell technologies to date. In a liquid variant of this

technology, efficiencies of up to 11% are currently being achieved (see, for example, Grätzel M. et al., J. Photochem. Photobio. C, 2003, 4, 145; Chiba et al., Japanese Journal of Appl. Phys., 2006, 45, L638-L640).

5 Dye solar cells, of which there are now several variants, generally have two electrodes, at least one of which is transparent. According to their function, the two electrodes are referred to as "working electrode" (also "anode", generation of electrons) and "counterelectrode" (also "cathode"). On the working electrode or in the vicinity thereof, an n-conductive metal oxide has generally been applied, especially as a porous, 10 for example nanoporous, layer, for example a nanoporous titanium dioxide (TiO_2) layer of thickness approx. 10-20 μm . Between the layer of the n-conductive metal oxide and the working electrode, it is additionally possible for at least one blocking layer to be provided, for example an impervious layer of a metal oxide, for example TiO_2 . The n-conductive metal oxide generally has an added light-sensitive dye. For example, on the surface of 15 the n-conductive metal oxide, a monolayer of a light-sensitive dye (for example a ruthenium complex) may be adsorbed, which can be converted to an excited state by absorption of light. At or on the counterelectrode, it is frequently a catalytic layer of a few μm in thickness, for example platinum. The area between the two electrodes in the conventional dye solar cell is generally filled with a redox electrolyte, for example a 20 solution of iodine (I_2) and/or potassium iodide (KI).

The function of the dye solar cell is based on absorption of light by the dye. From the excited dye, electrons are transferred to the n-semiconductive metal oxide semiconductor and migrate thereon to the anode, whereas the electrolyte ensures 25 charge balance via the cathode. The n-semiconductive metal oxide, the dye and the electrolyte are thus the essential constituents of the dye solar cell.

However, the dye solar cell produced with liquid electrolyte in many cases suffers from nonoptimal sealing, which can lead to stability problems. The liquid redox electrolyte can 30 especially be replaced by a solid p-semiconductor. Such solid dye solar cells are also referred to as sDSCs (solid DSCs). The efficiency of the solid variant of the dye solar cell is currently approx. 4.6 – 4.7% (Snaith, H., Angew. Chem. Int. Ed., 2005, 44, 6413-6417).

35 Various inorganic p-semiconductors such as CuI , $CuBr \cdot 3(S(C_4H_9)_2)$ or $CuSCN$ have been used to date in dye solar cells in place of the redox electrolyte. It is also possible, for example, to apply findings from photosynthesis. In nature too, it is the $Cu(I)$ enzyme plastocyanine which, in photosystem I, reduces the oxidized chlorophyll dimer again. Such p-semiconductors can be processed by means of at least three different methods,

namely: from a solution, by electrodeposition or by laser deposition.

Organic polymers have also already been used as solid p-semiconductors. Examples thereof include polypyrrole, poly(3,4-ethylenedioxythiophene), carbazole-based 5 polymers, polyaniline, poly(4-undecyl-2,2'-bithiophene), poly(3-octylthiophene), poly(triphenyldiamine) and poly(N-vinylcarbazole). In the case of poly(N-vinylcarbazole), the efficiencies extend up to 2%. PEDOT (poly(3,4-ethylenedioxythiophene) polymerized in situ also showed an efficiency of 0.53%. The polymers described here are typically not used in pure form, but rather with additives.

10 Inorganic-organic mixed systems have also already been used in place of the redox electrolyte in dye solar cells. For example, CuI was used together with PEDOT:PSS as a hole conductor in sDSC (Zhang J. Photochem: Photobio., 2007, 189, 329).

15 It is also possible to use low molecular weight organic p-semiconductors, i.e. nonpolymerized, for example monomeric or else oligomeric, organic p-semiconductors. The first use of a low molecular weight p-semiconductor in solid dye solar cells replaced the liquid electrolyte with a vapor-deposited layer of triphenylamine (TPD). The use of 20 the organic compound 2,2',7,7'-tetrakis(N,N-di-p-methoxyphenylamine)-9,9'-spiro-bifluorene (spiro-MeOTAD) in dye solar cells was reported in 1998. It can be introduced from a solution and has a relatively high glass transition temperature, which prevents unwanted crystallization and poor contact to the dye. The methoxy groups adjust the oxidation potential of spiro-MeOTAD such that the Ru complex can be regenerated 25 efficiently. In the case of use of spiro-MeOTAD alone as a p-semiconductor, a maximum IPCE (incident photon to current conversion efficiency, external photon conversion efficiency) of 5% was found. When $N(PhBr)_3SbCl_6$ as a dopant, and $Li[CF_3SO_2]_2N$ were also used, the IPCE rose to 33%, and the efficiency was 0.74%. The use of tert-30 butylpyridine as a solid p-semiconductor increased the efficiency to 2.56%, with an open-circuit voltage (V_{oc}) of approx. 910 mV and a short-circuit current I_{sc} of approx. 5 mA at an active area of approx. 1.07 cm^2 (see Krüger et al., Appl. Phys. Lett., 2001, 79, 2085). Dyes which achieved better coverage of the TiO_2 layer and which have good wetting on spiro-MeOTAD show efficiencies of more than 4%. Even better efficiencies (approx. 4.6%) were reported when the ruthenium complex was equipped with oxyethylene side chains.

35 L. Schmidt-Mende *et al.*, Adv. Mater. 17, p. 813-815 (2005) proposed an indoline dye for dye solar cells with spirobifluorenes as the amorphous organic p-conductor. This organic dye, which has an extinction coefficient four times higher than a ruthenium complex, exhibits a high efficiency (4.1% at one sun) in solid dye solar cells. In addition, a concept

was presented, in which polymeric p-semiconductors are bonded directly to an Ru dye (Peter, K., Appl. Phys. A. 2004, 79, 65). Durrant *et al.* Adv. Munc. Mater. 2006, 16, 1832-1838 state that, in many cases, the photocurrent is directly dependent on the yield at the hole transition from the oxidized dye to the solid p-conductor. This depends on two factors: firstly on the degree of penetration of the p-semiconductor into the oxide pores, and secondly on the thermodynamic driving force for the charge transfer (i.e. especially the difference in the free enthalpy ΔG between dye and p-conductor).

One disadvantage of the dye solar cell is that the proportion of light which can be used by the dye is generally limited by the energetic distance between the Fermi energies of the n- and p-conductors used. The photovoltage is generally also limited by this distance. In addition, dye solar cells generally have to be comparatively thin due to the charge transport required (for example 1-2.5 micrometers), such that the exploitation of the incident light is generally not optimal.

The prior art discloses that the addition of silver nitrate (AgNO_3) to the dye solution can lead to a rise in the solar cell efficiency (J. Krueger, Thesis, EPFL Lausanne, 2003 (Thesis No. 2793), p. 76-100). The general use of silver in oxidized form as a dopant for the p-semiconductor is not described.

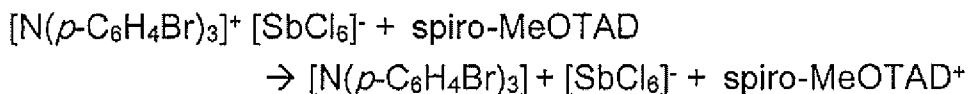
The electric and photoelectric properties of dye solar cells with different low molecular weight p-semiconductors has been examined in various further studies. One example thereof can be found in U. Bach, thesis, EPFL Lausanne, 2000 (Thesis No. 2187), and therein especially at pages 139-149. One feature examined here is the conductivity of spiro-MeOTAD, which is very low. For instance, in films with a layer thickness of approx. 2 micrometers, resistivities of $\text{M}\Omega/\text{cm}^2$ were measured. The conductivity κ is defined by

$$\kappa = \mu N_h e \quad (1).$$

In this formula, $e = 1.6022 \times 10^{-19} \text{ C}$, the elementary charge of an electron or hole. μ denotes the charge carrier mobility, and N_h the charge density, in this case of the holes. Assuming that the mobility does not change, in the case of a p-material, the conductivity rises as a result of the addition of further holes, i.e. in the case of p-doping. The result of this is that the fill factors of sDSCs are not very high, in particular at light intensities which are not low. The fill factor in photovoltaics generally refers to the quotient of the maximum power of a solar cell at the point of maximum power and the product of the open-circuit voltage and the short-circuit current. In the current-voltage diagram, the fill factor can frequently be described as the area ratio of a maximum rectangle inscribed

below the current-voltage curve to a minimum rectangle which encloses the curve. The fill factor is unitless. A low fill factor generally indicates that some of the power generated is being lost because of the internal resistance of the cell. In the above-described case of spiro-MeOTAD, the comparatively low fill factors are thus explained especially by the 5 high specific resistivity of the spiro-MeOTAD, as also described, for example, in F. Fabregat-Santiago *et al.*, J. Am. Chem. Soc., 2009, 131 (2), 558-562, especially at an illumination of one sun.

10 The prior art also discloses doping of low molecular weight organic p-semiconductors. For example, in U. Bach, thesis, EPFL Lausanne, 2000 (Thesis No. 2187), p. 37-50, antimony salts are used as dopants for spiro-MeOTAD. The doping operation can be described chemically as follows:



15 A concentration of 0.26 – 0.33 mM Sb was used, with a proportion of 0.17-0.18 M of spiro compounds. Even though the conductivity rises, the hole mobility was reduced as a result of the addition of the anions, which worsen the charge transport. In addition, the stability of such antimony salts in the cells was questioned.

20 N. Rossier-Iten, thesis, EPFL Lausanne, 2006 Thesis No. 3457), especially p. 56-75 and p. 91-113, also examined various doped hole conductor materials. The dopants used for an amorphous hole conductor in sDSCs therein included I₂, 2,3-dichloro-5,6-dicyano-1,4-benzoquinone, NOBF₄, and also a doped spiro diradical cation (spiro-MeOTAD⁺⁺ [PF₆]₂ 25 (0.1-0.7%). However, a decisive improvement in the sDSC cells was not achieved.

30 In Snaith *et al.*, Appl. Phys. Lett. 2006, 89, 262114-262116, it was found that the mobilities of holes in sDSCs are greatly improved by the addition of lithium bis(trifluoromethylsulfonyl)amine (Li-TFSI). Thus, it was possible to increase the mobilities from 1.6×10^{-4} cm²/Vs to 1.6×10^{-3} cm²/Vs, even though no oxidation of spiro-MeOTAD is observed here, i.e. no actual doping effect. It was found that the conductivity of spiro-MeOTAD is influenced to a lesser extent by the antimony salt, and that the best sDSC cells are even achieved without such a salt, since the anions act as what are called Coulomb traps (charge carrier traps).

35 Typically, an amount of more than 1 mol% of dopant is required in order to improve the charge mobility of an amorphous p-conductor.

Organic p-dopants, for example F4-TCNQ (tetrafluorotetracyanoquinodimethane) have also already been used with organic polymers of the p type (see, for example, R. Friend *et al.*, *Adv. Mater.*, 2008, 20, 3319-3324, Zhang *et al.*, *Adv. Funct. Mater.*, 2009, 19, 1901-1905). What is called protic doping of polythiophene by alkylsilanes has also been reported (see Podzorov *et al.*, *Advanced Functional Materials* 2009, 19, 1906-1911). Components with organic dopants, however, have comparatively low lifetimes in many cases.

It is additionally known that SnCl_5 and FeCl_3 are also usable as p-dopants. In addition, polymers, such as PEDOT, doped with LiCF_3SO_3 , LiBF_4 , LiTFSI and LiClO_4 , for example, have also been used as hole conductors in sDSCs. In the case of such components too, however, comparatively low external power efficiencies of up to 2.85% were recorded (Yanagida *et al.*, *JACS*, 2008, 130, 1258-1263).

In addition, the use of metal oxides as dopants is also known from the prior art, for example from DE 10 2007 024 153 A1 or DE 10 2007 023 876 A1. Metal oxides are vapor-deposited in organic layers and serve as dopants therein. An example mentioned is that of phenanthroline derivatives as a complex-forming matrix material, which are doped, for example, with rhenium oxides.

In addition, studies on the doping of organic p-transport materials for organic light-emitting diodes by means of vapor-deposited inorganic compounds are also known, for example from Kim *et al.*, *Appl. Phys. Lett.* 2007, 91, 011113(1-3). Here, for example, NPB was doped with ReO_3 (8-25%), which led to lower use voltages (turn-on voltages) and higher power efficiencies. The stability of the OLEDs was likewise improved. Kim *et al.*, *Org. Elec.* 2008, 805-808 state that hole injection layers have been doped with CuI . This doping too led to higher current efficiencies and energy efficiencies. Kim *et al.*, *Appl. Phys. Lett.* 2009, 94, 123306 (1-3) compare CuI , MoO_3 and ReO_3 as dopants for organic light-emitting diodes (OLEDs). A trend is found here to the effect that the energy difference between the HOMO (highest occupied molecular orbital) of the organic p-semiconductor and the Fermi level of the dopants plays an important role. Overall, it was found that the dopants increase the charge carrier densities and hence the conductivities in the transport layers, which is equivalent to p-doping.

Kahn *et al.*, *Chem. Mater.* 2010, 22, 524-531 also discloses that molybdenum dithiolene ($\text{Mo}(\text{fd})_3$) in a concentration of 0-3.8 mol% can dope various hole conductors. By means of UPS experiments (UV photoelectron spectroscopy), it was shown that the Fermi level of the hole conductor has been shifted in the direction of the HOMO, which is an

indication of p-doping.

Kowalsky *et al.*, Org. Elec. 2009, 10, 932-938 report that Mo_3O_9 clusters of vapor-deposited MoO_3 probably arise, and can also play a role in doping. In addition, the Fermi level (6.86 eV) and the electron affinity (6.7 eV) were measured at a much lower level than previously assumed. It was also speculated (cf. Kanai *et al.*, Organic Electronics 2010, 11, 188-194) that MoO_3 layers can readily be n-doped by oxygen defect sites, which leads to an improved alignment of the bands with respect to one another.

The use of pure layers of metal oxides, for example MoO_3 and V_2O_5 , is also described for OLEDs and for organic solar cells, in order to improve hole injection or hole extraction from the/into the electrode. For example, Y. Yang *et al.*, Appl. Phys. Lett. 2006, 88, 073508 examine the use of V_2O_5 , MoO_3 and PEDOT:PSS as an intermediate layer between ITO (indium tin oxide) and a p-type polymer. In what are called inverted polymer cells too, in which holes should migrate from the p-type polymer into the cathode (in this case generally Ag), a VO_x layer was vapor-deposited between the polymer and the silver, which led to an improvement in the properties of the cell.

In addition, the production of metal oxide buffer layers from an aqueous solution is also known. For example, Liu SESMC, 2010, 842-845, vol. 94 states that MoO_3 layers have been used successfully as a buffer layer on the anode in polymer solar cells. Such layers have also been used as part of a charge recombination layer in what are called organic tandem solar cells (see, for example, Kowalsky *et al.*, Adv. Func. Mater. 2010, 20, 1762-1766).

Since no efficient, soluble and stable p-dopant for hole transport materials is yet known in general terms, in the last few years, dye solar cells have in practice been stored under air (ambient conditions) in many cases. Oxygen which penetrates into the sDSCs in the course thereof dopes the sDSC. The storage of cells in an ambient atmosphere or in a controlled O_2 atmosphere is, however, less reproducible and comparatively problematic with regard to commercial production of solar modules. In addition, it is impossible to encapsulate oxygen-doped cells in an airtight manner, since a high conductivity of the whole conductor, which is needed for operation, is ensured only with constant contact to oxygen.

Advantages of the invention

Advantageously the present invention may provide a photovoltaic element and a process for producing a photovoltaic element, which at least substantially avoid the

disadvantages of known photovoltaic elements and production processes. More particularly, a photovoltaic element will be specified, which has a p-semiconductor with a high conductivity, as will a process for doping p-semiconductors and a stable p-dopant which, even with exclusion of oxygen, brings about stable p-doping of organic materials 5 for dye solar cells. At the same time, a dye solar cell which is stable even in the encapsulated state and has a high quantum efficiency and a high fill factor would be desirable, nevertheless being simple to produce.

Disclosure of the invention

10 This object is achieved by the invention with the features of the independent claims. Advantageous developments, which can be implemented individually or in any combination, are described in the dependent claims.

15 In a first aspect of the present invention, a photovoltaic element for conversion of electromagnetic radiation to electrical energy is proposed, more particularly a dye solar cell. The photovoltaic element comprises at least one first electrode, at least one n-semiconductive metal oxide, at least one dye which absorbs electromagnetic radiation, at least one solid organic p-semiconductor and at least one second electrode, preferably 20 (but not necessarily) in the sequence described or a reverse sequence, the p-semiconductor comprising silver in oxidized form.

25 The p-semiconductor may especially be producible or have been produced by applying at least one p-semiconductive organic material (128) and silver in oxidized form to at least one carrier element, the silver in oxidized form preferably being applied in the form of at least one silver(I) salt $[Ag^+]_m[A^{m-}]$ to at least one carrier element, where A^{m-} is the anion of an organic or inorganic acid, and m is an integer in the range from 1 to 3, preferably where m is 1.

30 $[A^{m-}]$ may especially be an anion of an organic acid, preferably where the organic acid has at least one fluorine group -F or cyano group (-CN). In this case, $[A^{m-}]$ more preferably has a structure of the formula (II)



35 where R^a is a fluorine group -F or an alkyl radical, cycloalkyl radical, aryl radical or heteroaryl radical each substituted by a fluorine group or a cyano group,

and where X is - O- or $\text{--N}^{\text{-}}\text{R}^{\text{b}}$,

and where R^{b} comprises a fluorine group - F or a cyano group,

5 and where R^{b} further comprises a group of the formula $-(\text{O})_2\text{-}$.

R^{a} may especially be selected from the group consisting of - F, $-\text{CF}_3$, $-\text{CF}_2\text{-CF}_3$ and $-\text{CH}_2\text{-CN}$.

10 X may especially be $\text{--N}^{\text{-}}\text{R}^{\text{b}}$, and R^{b} may especially be selected from the group consisting of - $\text{S}(\text{O})_2\text{- F}$, $-\text{S}(\text{O})_2\text{-CF}_3$, $-\text{S}(\text{O})_2\text{-CF}_2\text{-CF}_3$ and $-\text{S}(\text{O})_2\text{-CH}_2\text{-CN}$.

15 $[\text{A}^{\text{m-}}]$ may especially be selected from the group consisting of: bis(trifluoromethylsulfonyl)imide (TFSI $^{\text{-}}$), bis(trifluoroethylsulfonyl)imide, bis(fluoro-sulfonyl)imide, trifluoromethylsulfonate.

Preferably, $[\text{A}^{\text{m-}}]$ is bis(trifluoromethylsulfonyl)imide (TFSI $^{\text{-}}$).

In an alternative preferred embodiment, $[\text{A}^{\text{m-}}]$ is a trifluoroacetate group.

20 In addition, $[\text{A}^{\text{m-}}]$ may especially also be an $\text{NO}_3^{\text{-}}$ group.

25 The application can be effected by any desired process. Preference is given to applying the at least one p-conductive organic material (128) and silver in the context of the invention by deposition from a liquid phase.

30 The p-semiconductor is preferably producible or produced by applying at least one p-conductive organic material (128) and at least silver, preferably the at least one silver(I) salt $[\text{Ag}^{\text{+}}]_m[\text{A}^{\text{m-}}]$, to at least one carrier element, the application being effected by deposition from a liquid phase comprising the at least one p-conductive organic material and the at least one silver(I) salt $[\text{Ag}^{\text{+}}]_m[\text{A}^{\text{m-}}]$.

35 The deposition can again in principle be effected by any desired deposition process, for example by spin-coating, knife-coating, printing or combinations of said and/or other deposition processes.

The p-semiconductor may especially comprise at least one organic matrix material, in which case the anionic compounds $[\text{A}^{\text{m-}}]$ and $\text{Ag}^{\text{+}}$ have been mixed into the matrix material or are present in the matrix material, especially in dissolved form.

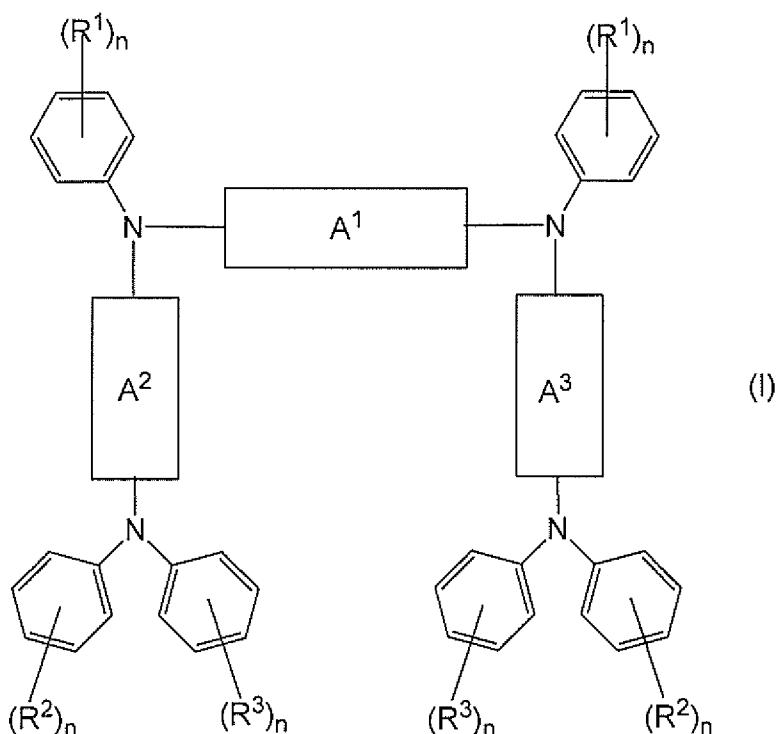
At least Ag^+ and preferably also the anionic compound $[\text{A}^{\text{m-}}]$ may especially be present in essentially homogeneous distribution in the matrix material.

5 The matrix material may especially comprise at least one low molecular weight organic p-semiconductor.

The low molecular weight organic p-semiconductor may especially comprise at least one spiro compound.

10

The low molecular weight organic p-semiconductor may especially be selected from: a spiro compound, especially spiro-MeOTAD; a compound with the structural formula:



15

in which

$\text{A}^1, \text{A}^2, \text{A}^3$ are each independently optionally substituted aryl groups or heteroaryl groups,

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$\text{R}^1, \text{R}^2, \text{R}^3$ are each independently selected from the group consisting of the substituents $-\text{R}$, $-\text{OR}$, $-\text{NR}_2$, $-\text{A}^4-\text{OR}$ and $-\text{A}^4-\text{NR}_2$,

where R is selected from the group consisting of alkyl, aryl and heteroaryl,

and

where A^4 is an aryl group or heteroaryl group, and

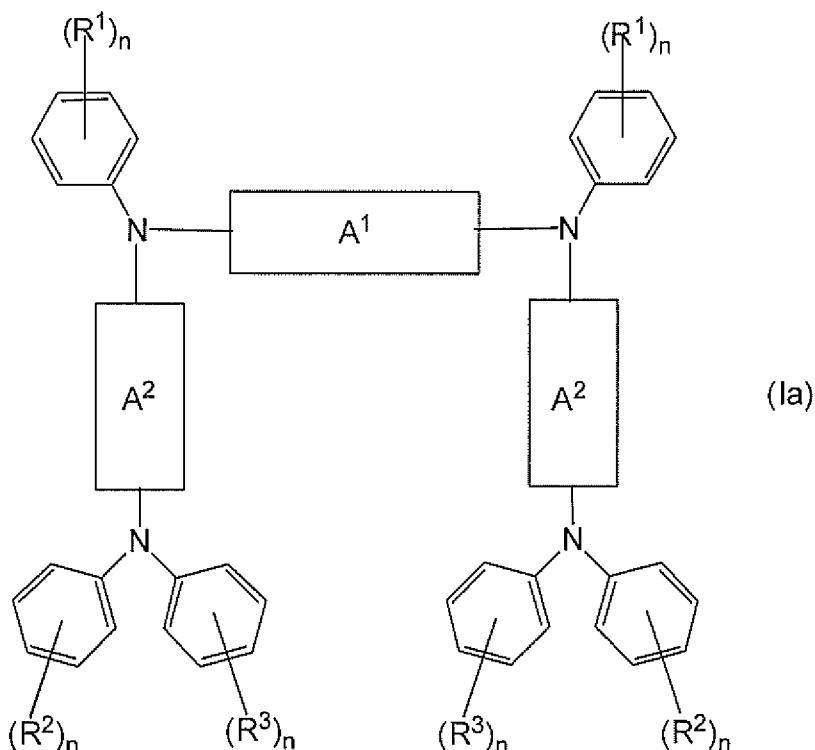
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where n at each instance in formula I is independently a value of 0, 1, 2 or 3,

with the proviso that the sum of the individual n values is at least 2 and at least two of the R^1 , R^2 and R^3 radicals are $-OR$ and/or $-NR_2$.

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Preferably, A^2 and A^3 are the same; accordingly, the compound of the formula (I) preferably has the following structure (Ia)



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The photovoltaic element may further comprise at least one encapsulation, the encapsulation being designed to shield the photovoltaic element, especially the electrodes and/or the p-semiconductor, from a surrounding atmosphere.

20 In a preferred embodiment, the p-semiconductor has been produced or is producible by applying at least one p-conductive organic material (128) and at least one silver(I) salt $[Ag^+]_m[A^{m-}]$ to at least one carrier element as described above, wherein the application can be effected by deposition from a liquid phase comprising the at least one p-conductive organic material and the at least one silver(I) salt $[Ag^+]_m[A^{m-}]$, and wherein

the liquid phase comprises the at least one silver(I) salt $[Ag^+]_m[A^{m-}]$ in a concentration of 0.5 mm/ml to 50 mm/ml, more preferably in a concentration of 1 mm/ml up to 20 mm/ml.

In a further aspect of the present invention, a process for producing a solid organic p-semiconductor for use in an organic component is proposed, more particularly a photovoltaic element according to one or more of the embodiments of a photovoltaic element according to the present invention which have been described above or are yet to be described. In the process, at least one p-conductive organic matrix material and at least silver in oxidized form, preferably at least one silver(I) salt $[Ag^+]_m[A^{m-}]$, are applied from at least one liquid phase to at least one carrier element, where $[A^-]$ is the anion of an organic or inorganic acid, and where the compound $[Ag^+]_m[A^{m-}]$ is preferably $AgNO_3$ or silver bis(trifluoromethylsulfonyl)imide.

The liquid phase may further comprise at least one solvent, especially an organic solvent, especially a solvent selected from the group consisting of cyclohexanone; chlorobenzene; benzofuran and cyclopentanone.

The process can especially be performed at least partly in a low-oxygen atmosphere, for example in an atmosphere comprising less than 500 ppm of oxygen, especially less than 100 ppm of oxygen and more preferably less than 50 ppm or even less than 10 ppm of oxygen.

In a further aspect of the present invention, a process for producing a photovoltaic element is proposed, especially a photovoltaic element according to one or more of the configurations of a photovoltaic element according to the present invention which have been described above or are yet to be described. In the process, at least one first electrode, at least one n-semiconductive metal oxide, at least one dye which absorbs electromagnetic radiation, at least one solid organic p-semiconductor and at least one second electrode are provided, especially (but not necessarily) in the sequence described or a reverse sequence, the p-semiconductor being produced by a process according to one or more of the configurations of a process according to the invention for producing a solid organic p-semiconductor which have been described above or are yet to be described.

It has been found in the context of the present invention that, surprisingly, silver in oxidized form can achieve efficient p-doping, especially in dye solar cells. Particularly efficient p-doping can be achieved especially by the use of a silver(I) salt of the formula $[Ag^+]_m[A^{m-}]$ where $[A^{m-}]$ is the anion of an organic or inorganic acid, and m is an integer in the range from 1 to 3. These silver(I) salts can be applied especially in a liquid phase by

means of one or more organic solvents, preferably together with a p-semiconductive matrix material and optionally one or more organic salts. In this way, it is possible to achieve photovoltaic elements with high fill factors and a high long-term stability.

5 In the abovementioned first aspect of the present invention, a photovoltaic element for conversion of electromagnetic radiation to electrical energy is thus proposed. The photovoltaic element may especially comprise one or more photovoltaic cells. The photovoltaic element may especially comprise at least one layer structure which may be applied, for example, to a substrate. The photovoltaic element may especially comprise
10 at least one dye solar cell and/or be configured as a dye solar cell.

The photovoltaic element has at least one first electrode, at least one n-semiconductive metal oxide, at least one electromagnetic radiation-absorbing dye, at least one solid organic p-semiconductor and at least one second electrode. It is proposed that the p-
15 semiconductor comprises silver in oxidized form.

The elements described may be provided especially in the sequence described. For example, the photovoltaic element may comprise, in the sequence described, the at least one first electrode, the at least one n-semiconductive metal oxide, the at least one electromagnetic radiation-absorbing dye, the at least one solid organic p-semiconductor and the at least one second electrode. However, the dye and the n-semiconductive metal oxide may also be completely or partially combined, as is customary in dye solar cells. For example, the n-semiconductive metal oxide may be completely or partially impregnated with the at least one dye, or mixed with this dye in some other way. In this way and/or in some other way, the n-semiconductive metal oxide can especially be sensitized with the dye, such that, for example, dye molecules can be applied as a monolayer to particles of the n-semiconductive metal oxide. For example, a direct contact may exist between the dye molecules and the n-semiconductive metal oxide, such that transfer of charge carriers is possible. The photovoltaic element may especially comprise at least one layer of the n-semiconductive metal oxide, optionally with the dye, and at least one layer of the solid organic p-semiconductor. This layer structure may be embedded between the electrodes. In addition, the photovoltaic element may comprise one or more further layers. For example, one or more further layers may be introduced between the first electrode and the n-semiconductive metal oxide, for example one or
20 more buffer layers, for example layers of a metal oxide. While the buffer layer is preferably impervious, the n-semiconductive metal oxide may especially be porous and/or particulate. More particularly, the n-semiconductive metal oxide, as will be described in detail hereinafter, may be configured as a nanoparticulate layer. In addition, it is also possible for one or more further layers to be provided between the n-
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semiconductive metal oxide and the solid organic p-semiconductor, and also optionally for one or more further layers to be provided between the p-semiconductor and the second electrode.

5 The p-semiconductor may especially be p-doped by the silver in oxidized form, preferably by the at least one silver(I) salt of the formula $[Ag^+]_m[A^{m-}]$. This means that the p-conductive properties of the p-semiconductor are obtained or enhanced by the silver in oxidized form, preferably by the at least one silver(I) salt of the formula $[Ag^+]_m[A^{m-}]$. More particularly, the silver in oxidized form, especially the at least one silver(I) salt of the
10 formula $[Ag^+]_m[A^{m-}]$, may be set up to dope the p-semiconductor or a matrix material present in this p-semiconductor. For example, the p-semiconductor may comprise at least one organic matrix material, in which case the silver in oxidized form, preferably the at least one silver(I) salt of the formula $[Ag^+]_m[A^{m-}]$, has been mixed into the matrix material. This is preferably achieved by applying both silver in oxidized form, preferably
15 at least one silver(I) salt of the formula $[Ag^+]_m[A^{m-}]$, and the organic matrix material to at least one carrier material.

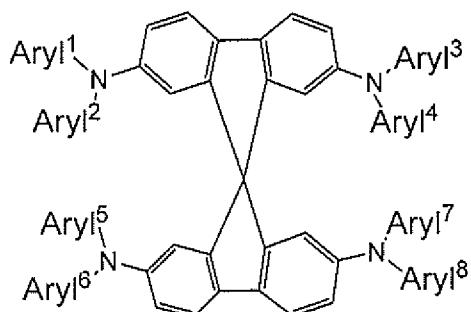
Accordingly, the present invention preferably relates to a photovoltaic element as described above, wherein the p-semiconductor is producible or has been produced by
20 applying at least one p-conductive organic material (128) and silver in oxidized form to at least one carrier element, the silver in oxidized form preferably being applied in the form of at least one silver(I) salt $[Ag^+]_m[A^{m-}]$ to at least one carrier element, where A^{m-} is the anion of an organic or inorganic acid, and m is an integer in the range from 1 to 3, preferably where m is 1.
25 The matrix material and the silver may be applied to the carrier material together or in separate steps. Preferably, the matrix material and the silver are applied together to the carrier material. "Applied together" or "applied jointly" in this context means that preferably a mixture G comprising both the matrix material is applied to the carrier material in at least one step, preferably in one step.

30 Preferably, the mixture G is a liquid phase. The term "liquid phase" in this context means that mixture G is present at least partly as a liquid. Preferably, mixture G or preferably the liquid phase comprises at least one solvent in which silver and the at least one organic matrix material are dissolved and/or dispersed, as described below. As
35 already stated above, the application is preferably effected by deposition from the liquid phase, and the deposition can again in principle be effected by any desired deposition process, for example by spin-coating, knife-coating, printing or combinations of said and/or other deposition processes.

The low molecular weight organic p-semiconductor:

More particularly, the matrix material may have at least one low molecular weight organic p-semiconductor. A low molecular weight material is generally understood to mean a material which is present in monomeric, nonpolymerized or nonoligomerized form. The term " low molecular weight" as used in the present context preferably means that the semiconductor has molecular weights in the range from 100 to 25 000 g/mol. Preferably, the low molecular weight substances have molecular weights of 500 to 2000 g/mol. These low molecular weight organic p-semiconductors may especially form the abovementioned matrix material and may intrinsically have p-semiconductive properties. In general, in the context of the present invention, p-semiconductive properties are understood to mean the property of materials, especially of organic molecules, to form holes and to transport these holes and to pass them on to adjacent molecules. More particularly, stable oxidation of these molecules should be possible. In addition, the low molecular weight organic p-semiconductors mentioned may especially have an extensive π -electron system. More particularly, the at least one low molecular weight p-semiconductor may be processable from a solution. The low molecular weight p-semiconductor may especially comprise at least one triphenylamine. It is particularly preferred when the low molecular weight organic p-semiconductor comprises at least one spiro compound. A spiro compound is understood to mean polycyclic organic compounds whose rings are joined only at one atom, which is also referred to as the spiro atom. More particularly, the spiro atom may be sp^3 -hybridized, such that the constituents of the spiro compound connected to one another via the spiro atom are, for example, arranged in different planes with respect to one another.

More preferably, the spiro compound has a structure of the following formula:

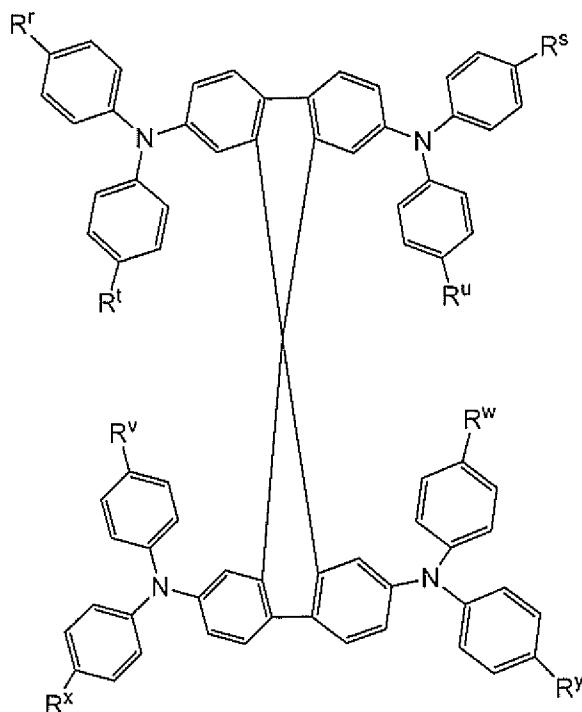


where the aryl¹, aryl², aryl³, aryl⁴, aryl⁵, aryl⁶, aryl⁷ and aryl⁸ radical are each independently selected from substituted aryl radicals and heteroaryl radicals, especially from substituted phenyl radicals, where the aryl radicals and heteroaryl radicals, preferably the phenyl radicals, are each independently substituted, preferably in each

case by one or more substituents selected from the group consisting of -O-alkyl, -OH, -F, -Cl, -Br and -I, where alkyl is preferably methyl, ethyl, propyl or isopropyl. More preferably, the phenyl radicals are each independently substituted, in each case by one or more substituents selected from the group consisting of -O-Me, -OH, -F, -Cl, -Br and -I.

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Further preferably, the spiro compound is a compound of the following formula:

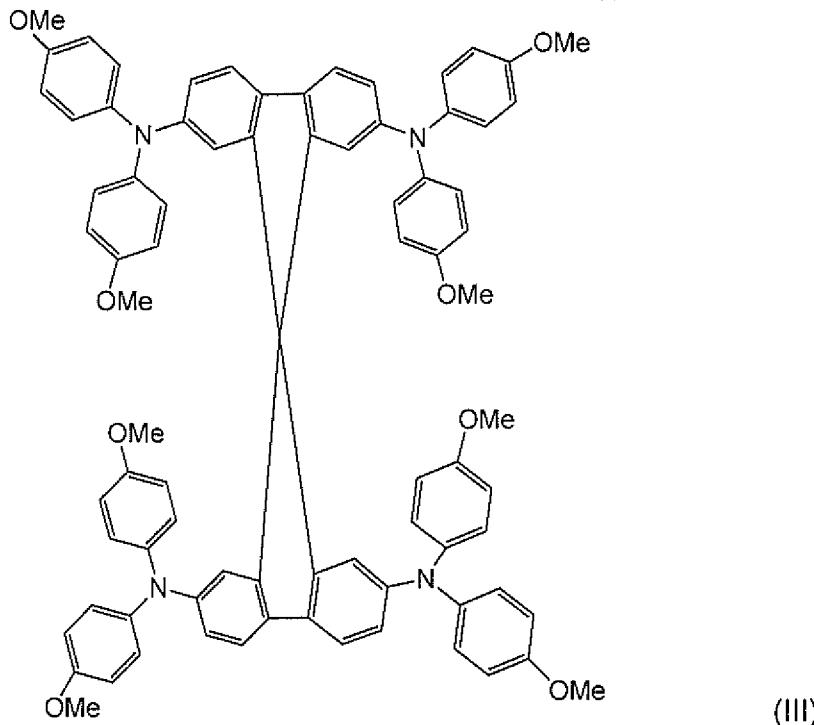


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where R^t, R^s, R^t, R^u, R^v, R^w, R^x and R^y are each independently selected from the group consisting of -O-alkyl, -OH, -F, -Cl, -Br and -I, where alkyl is preferably methyl, ethyl, propyl or isopropyl. More preferably, R^t, R^s, R^t, R^u, R^v, R^w, R^x and R^y are each independently selected from the group consisting of -O-Me, -OH, -F, -Cl, -Br and -I.

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More particularly, the p-semiconductor or the matrix material may comprise spiro-MeOTAD or consist of spiro-MeOTAD, i.e. a compound of the formula (III) commercially available, for example, from Merck KGaA, Darmstadt, Germany, Taiwan:



(III)

Alternatively or additionally, it is also possible to use other p-semiconductive compounds, especially low molecular weight and/or oligomeric and/or polymeric p-semiconductive

5 compounds.

In an alternative embodiment, the low molecular weight organic p-semiconductor or the matrix material comprises one or more compounds of the abovementioned general formula I, for which reference may be made, for example, to PCT application number
10 PCT/EP2010/051826, which will be published after the priority date of the present application.

The p-semiconductor may comprise the at least one compound of the abovementioned general formula I additionally or alternatively to the spiro compound described above.

15 The term "alkyl" or "alkyl group" or "alkyl radical" as used in the context of the present invention is understood to mean substituted or unsubstituted C₁-C₂₀-alkyl radicals in general. Preference is given to C₁- to C₁₀-alkyl radicals, particular preference to C₁- to C₈-alkyl radicals. The alkyl radicals may be either straight-chain or branched. In
20 addition, the alkyl radicals may be substituted by one or more substituents selected from the group consisting of C₁-C₂₀-alkoxy, halogen, preferably F, and C₆-C₃₀-aryl which may in turn be substituted or unsubstituted. Examples of suitable alkyl groups are methyl, ethyl, propyl, butyl, pentyl, hexyl, heptyl and octyl, and also isopropyl, isobutyl, isopentyl, sec-butyl, tert-butyl, neopentyl, 3,3-dimethylbutyl, 2-ethylhexyl, and also derivatives of

the alkyl groups mentioned substituted by C₆-C₃₀-aryl, C₁-C₂₀-alkoxy and/or halogen, especially F, for example CF₃.

5 The term " aryl" or " aryl group" or " aryl radical" as used in the context of the present invention is understood to mean optionally substituted C₆-C₃₀-aryl radicals which are derived from monocyclic, bicyclic, tricyclic or else multicyclic aromatic rings, where the aromatic rings do not comprise any ring heteroatoms. The aryl radical preferably comprises 5- and/or 6-membered aromatic rings. When the aryls are not monocyclic systems, in the case of the term "aryl" for the second ring, the saturated form (perhydro form) or the partly unsaturated form (for example the dihydro form or tetrahydro form), provided the particular forms are known and stable, is also possible. The term "aryl" in the context of the present invention thus comprises, for example, also bicyclic or tricyclic radicals in which either both or all three radicals are aromatic, and also bicyclic or tricyclic radicals in which only one ring is aromatic, and also tricyclic radicals in which two 10 rings are aromatic. Examples of aryl are: phenyl, naphthyl, indanyl, 1,2-dihydronaphthyl, 1,4-dihydronaphthyl, fluorenyl, indenyl, anthracenyl, phenanthrenyl or 1,2,3,4-tetrahydronaphthyl. Particular preference is given to C₆-C₁₀-aryl radicals, for example phenyl or naphthyl, very particular preference to C₆-aryl radicals, for example phenyl. In addition, the term " aryl" also comprises ring systems comprising at least 15 two monocyclic, bicyclic or multicyclic aromatic rings joined to one another via single or double bonds. One example is that of biphenyl groups.

20 The term " heteroaryl" or " heteroaryl group" or " heteroaryl radical" as used in the context of the present invention is understood to mean optionally substituted 5- or 6-membered aromatic rings and multicyclic rings, for example bicyclic and tricyclic compounds having at least one heteroatom in at least one ring. The heteroaryls in the context of the invention preferably comprise 5 to 30 ring atoms. They may be 25 monocyclic, bicyclic or tricyclic, and some can be derived from the aforementioned aryl by replacing at least one carbon atom in the aryl base skeleton with a heteroatom. Preferred heteroatoms are N, O and S. The hetaryl radicals more preferably have 5 to 13 30 ring atoms. The base skeleton of the heteroaryl radicals is especially preferably selected from systems such as pyridine and five-membered heteroaromatics such as thiophene, pyrrole, imidazole or furan. These base skeletons may optionally be fused to one or two six-membered aromatic radicals. In addition, the term " heteroaryl" also comprises ring 35 systems comprising at least two monocyclic, bicyclic or multicyclic aromatic rings joined to one another via single or double bonds, where at least one ring comprises a heteroatom. When the heteroaryls are not monocyclic systems, in the case of the term " heteroaryl" for at least one ring, the saturated form (perhydro form) or the partly unsaturated form (for example the dihydro form or tetrahydro form), provided the

particular forms are known and stable, is also possible. The term "heteroaryl" in the context of the present invention thus comprises, for example, also bicyclic or tricyclic radicals in which either both or all three radicals are aromatic, and also bicyclic or tricyclic radicals in which only one ring is aromatic, and also tricyclic radicals in which two 5 rings are aromatic, where at least one of the rings, i.e. one aromatic or one nonaromatic ring has a heteroatom. Suitable fused heteroaromatics are, for example, carbazolyl, benzimidazolyl, benzofuryl, dibenzofuryl or dibenzothiophenyl. The base skeleton may be substituted at one, more than one or all substitutable positions, suitable substituents being the same as have already been specified under the definition of C₆-C₃₀-aryl. 10 However, the hetaryl radicals are preferably unsubstituted. Suitable hetaryl radicals are, for example, pyridin-2-yl, pyridin-3-yl, pyridin-4-yl, thiophen-2-yl, thiophen-3-yl, pyrrol-2-yl, pyrrol-3-yl, furan-2-yl, furan-3-yl and imidazol-2-yl and the corresponding benzofused radicals, especially carbazolyl, benzimidazolyl, benzofuryl, dibenzofuryl or dibenzothiophenyl. 15

15 In the context of the invention the term "optionally substituted" refers to radicals in which at least one hydrogen radical of an alkyl group, aryl group or heteroaryl group has been replaced by a substituent. With regard to the type of this substituent, preference is given to alkyl radicals, for example methyl, ethyl, propyl, butyl, pentyl, hexyl, heptyl and 20 octyl, and also isopropyl, isobutyl, isopentyl, sec-butyl, tert-butyl, neopentyl, 3,3-dimethylbutyl and 2-ethylhexyl, aryl radicals, for example C₆-C₁₀-aryl radicals, especially phenyl or naphthyl, most preferably C₆-aryl radicals, for example phenyl, and hetaryl radicals, for example pyridin-2-yl, pyridin-3-yl, pyridin-4-yl, thiophen-2-yl, thiophen-3-yl, 25 pyrrol-2-yl, pyrrol-3-yl, furan-2-yl, furan-3-yl and imidazol-2-yl, and also the corresponding benzofused radicals, especially carbazolyl, benzimidazolyl, benzofuryl, dibenzofuryl or dibenzothiophenyl. Further examples include the following substituents: 30 alkenyl, alkynyl, halogen, hydroxyl.

30 The degree of substitution here may vary from monosubstitution up to the maximum number of possible substituents.

Preferred compounds of the formula I for use in accordance with the invention are notable in that at least two of the R¹, R² and R³ radicals are para-OR and/or -NR₂ substituents. The at least two radicals here may be only -OR radicals, only -NR₂ radicals, 35 or at least one -OR and at least one -NR₂ radical.

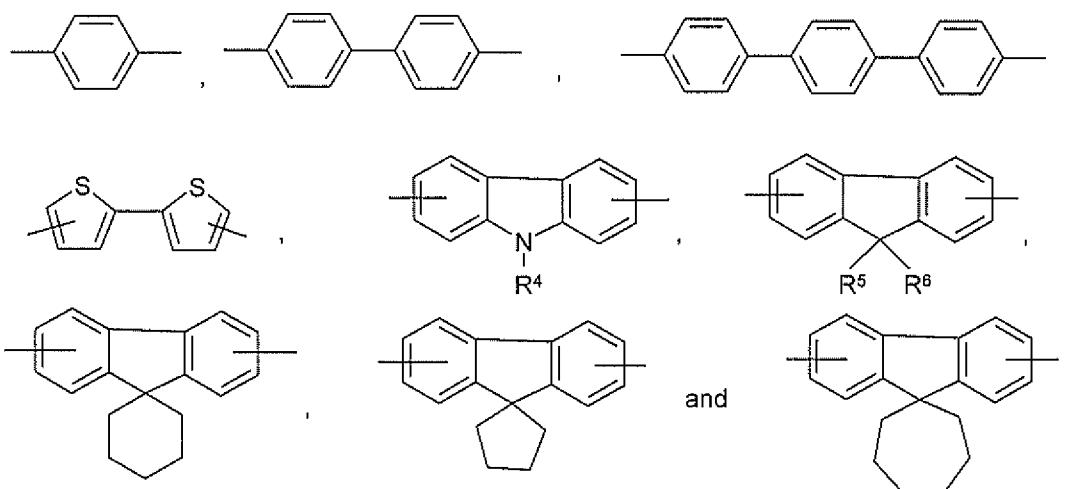
Particularly preferred compounds of the formula I for use in accordance with the invention are notable in that at least four of the R¹, R² and R³ radicals are para-OR

and/or $-\text{NR}_2$ substituents. The at least four radicals here may be only $-\text{OR}$ radicals, only $-\text{NR}_2$ radicals or a mixture of $-\text{OR}$ and $-\text{NR}_2$ radicals.

Very particularly preferred compounds of the formula I for use in accordance with the invention are notable in that all of the R¹, R² and R³ radicals are para-OR and/or -NR₂ substituents. They may be only -OR radicals, only -NR₂ radicals or a mixture of -OR and -NR₂ radicals.

In all cases, the two R in the $-\text{NR}_2$ radicals may be different from one another, but they are preferably the same.

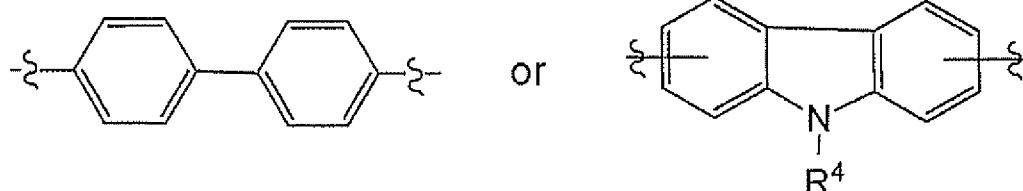
Preferably, A1, A2 and A3 are each independently selected from the group consisting of



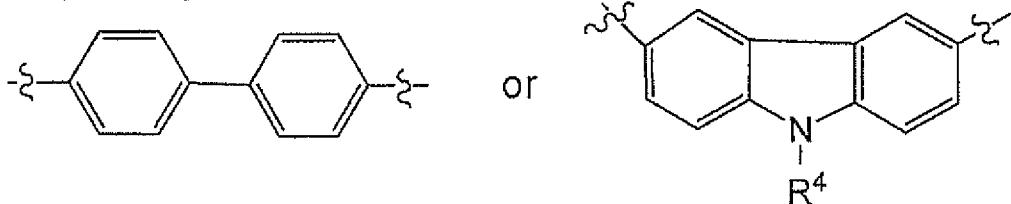
Preferred substituents in the case of further substitution of the aromatic and heteroaromatic rings include the substituents already mentioned above for the one, two or three optionally substituted aromatic or heteroaromatic groups.

5 Preferably, the aromatic and heteroaromatic rings of the structures shown do not have further substitution.

More preferably, A¹, A² and A³ are each independently

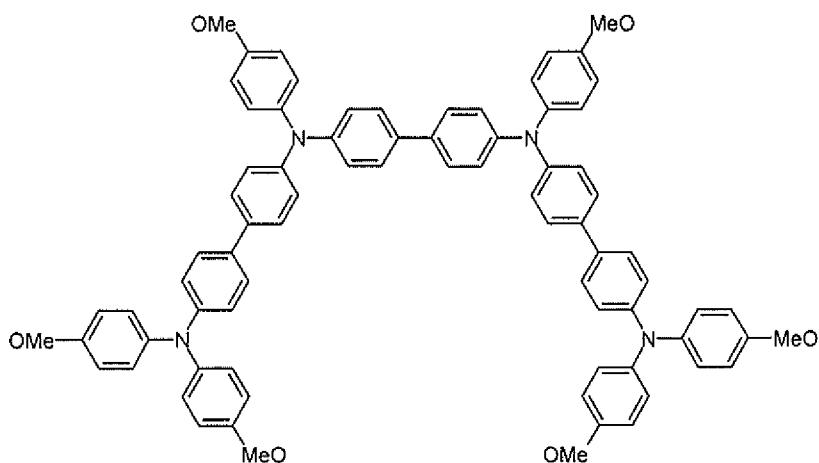


10 more preferably

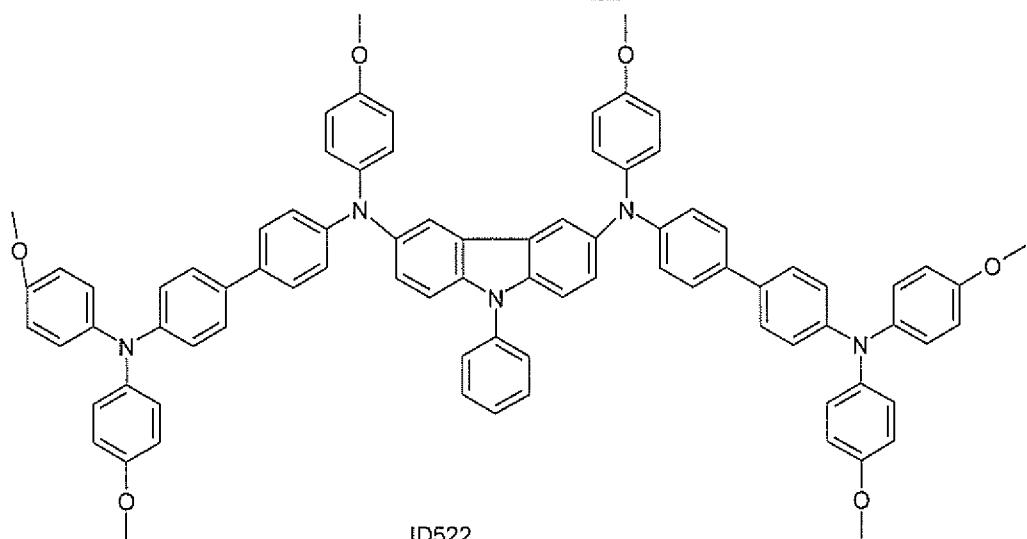


More preferably, the at least one compound of the formula (I) has one of the following structures:

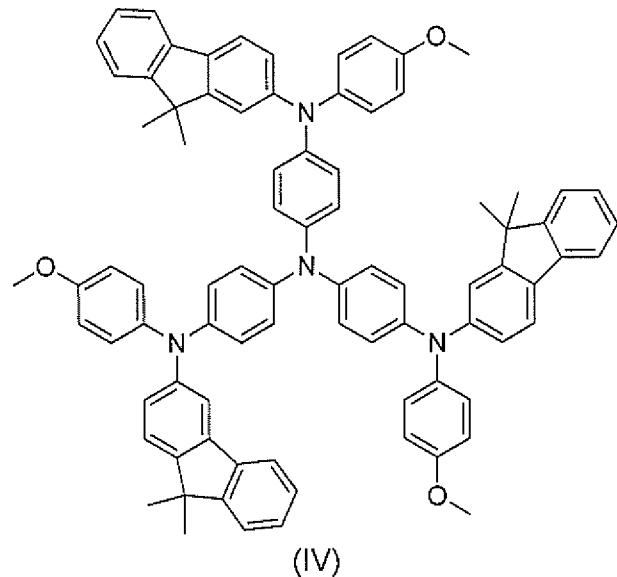
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ID367



In an alternative embodiment, the matrix material is ID322, i.e. a compound of the formula (IV):



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The compounds for use in accordance with the invention can be prepared by customary methods of organic synthesis known to those skilled in the art. References to relevant 10 (patent) literature can additionally be found in the synthesis examples adduced below.

At least one of the electrodes may be transparent. For example, the first electrode may be the working electrode and the second electrode the counterelectrode, or vice versa. One or both of these electrodes may be transparent. The photovoltaic element may 15 especially comprise at least one layer structure applied to a substrate, in which case the layer structure may comprise the first electrode, the n-semiconductive metal oxide, the dye, the solid organic p-semiconductor with the metal oxide and the at least one second electrode in the sequence mentioned, or in reverse sequence.

The n-semiconductive metal oxide may especially be porous, in which case, at least one buffer layer of a metal oxide may especially be introduced between the n-semiconductive metal oxide and the first electrode. This buffer layer may be, for example, an impervious 5 layer, i.e. a nonparticulate layer. For example, this buffer layer may be applied by means of a PVD process, for example a vapor deposition process and/or a sputtering process. Alternatively or additionally, it is also possible to use other processes, for example CVD processes and/or spray pyrolysis processes. The n-semiconductive metal oxide is, in contrast, preferably applied by means of a paste process, for example by print 10 application, spin-coating application or knife-coating application of a paste of an n-semiconductive metal oxide. This paste can subsequently be sintered by at least one thermal treatment step, for example by heating to more than 200°C, especially to more than 15 400°C, for example 450°C. This sintering can, for example, remove volatile constituents of the paste, such that preferably only the n-semiconductive metal oxide particles remain.

As described above, the dye can especially be applied to the n-semiconductive metal oxide. This application is preferably effected in such a way that the dye completely or partially penetrates an n-semiconductive metal oxide layer, for example a particulate 20 layer, in order to sensitize the particles of the n-semiconductive metal oxide, for example by virtue of one or more layers of the dye being formed on these particles, for example monomolecular layers. The application of the dye can accordingly be effected, for example, by means of at least one impregnation process, by, for example, immersing a sample comprising the n-semiconductive metal oxide layer into a solution of the dye. 25 Other impregnation processes are also usable.

As a particular advantage of the present invention, the photovoltaic element may especially comprise at least one encapsulation. In contrast to conventional photovoltaic elements, in which solid p-semiconductors are doped by means of oxygen (for example 30 by storage under air), the p-semiconductors doped with the silver in oxidized form, for example the at least one silver(I) salt $[Ag^+]_m[A^{m-}]$ and especially preferably silver bis(trifluoromethylsulfonyl)imide, may also exist without such an oxygen atmosphere over a prolonged period. Accordingly, it is possible to apply an encapsulation which screens the photovoltaic element, especially the electrodes and/or the p-semiconductor, 35 from a surrounding atmosphere. In this way, in spite of the improvement in properties of the p-semiconductor by virtue of the doping by means of the silver in oxidized form, especially the at least one silver(I) salt $[Ag^+]_m[A^{m-}]$ and especially preferably silver bis(trifluoromethylsulfonyl)imide, oxygen can be excluded, which protects, for example, one or more of the electrodes from adverse effects resulting from oxygen and/or other

surrounding gases. For example, the electrode degradation can be prevented in this way. The encapsulation may, for example, comprise encapsulation by a solid capsule element, for example a plane or capsule equipped with at least one depression, which is applied to the layer structure, for example, in such a way that it completely or partially surrounds the layer structure. For example, an edge of the encapsulation may completely or partially surround the layer structure and, for example, may be bonded to the substrate by an adhesive bond and/or another bond, preferably a cohesive bond. Alternatively or additionally, the encapsulation may also comprise one or more layers of a material which prevents penetration of harmful environmental influences, for example moisture and/or oxygen. For example, organic and/or inorganic coatings can be applied to the layer structure. Screening from ambient atmosphere can generally be understood to mean slowing of the penetration of gases and/or moisture from the surrounding atmosphere into the layer structure. The slowing can be effected, for example, in such a way that concentration differences within and outside the encapsulation are balanced out only within several hours, preferably several days, especially even several weeks, months extending up to years.

The dye solar cell may additionally have, between the n-semiconductive metal oxide and the p-semiconductor, especially at least one passivation material. This passivation material may especially be set up to at least partly prevent electron transfer between the n-semiconductive metal oxide and the p-semiconductor. The passivation material may especially be selected from: Al_2O_3 ; a silane, especially CH_3SiCl_3 ; an organometallic complex, especially an Al^{3+} complex, a 4-tert-butylpyridine; hexadecylmalonic acid.

As detailed above, in a further aspect of the present invention, a process is proposed for producing a solid organic p-semiconductor for use in an organic component. This organic component may especially be a photovoltaic element, for example a photovoltaic element in one or more of the above-described configurations, especially a dye solar cell. However, other configurations of the organic component are also possible in principle, including the end use in organic light-emitting diodes, organic transistors, and other types of photovoltaic elements, for example organic solar cells.

In the process proposed, at least one p-conductive organic matrix material, for example a matrix material of the type described above, and at least silver in oxidized form, preferably at least one silver(I) salt of the formula $[\text{Ag}^+]_m[\text{A}^m]_n$, are applied to at least one carrier element from at least one liquid phase. As described above, a p-conductive organic matrix material is understood to mean an organic material which can preferably be applied from solution and which is capable of transporting positive charges. These positive charges may already be present in the matrix material and merely be increased

by the p-doping, or can also actually be obtained as a result of the p-doping by means of the silver in oxidized form. More particularly, the matrix material may be stably and reversibly oxidizable and be set up to pass positive charges (" holes") on to other molecules, for example adjacent molecules of the same type.

5 In general, it is pointed out in this regard that the effect of the silver salt is based merely on observable effects of an increase in the p-conductivity. Accordingly, it is possible, for example, to increase a charge carrier density and/or a mobility of positive charges in the p-semiconductor by addition of the silver in oxidized form. The invention is not limited to
10 the way in which the p-doping is effected at the microscopic level.

15 The at least one organic matrix material and the silver in oxidized form, especially the at least one silver(I) salt of the formula $[Ag^+]_m[A^{m-}]$, as a p-dopant are preferably applied together to the at least one carrier element from at least one liquid phase, as described above. A carrier element may be understood to mean a pure substrate, for example a
20 glass and/or plastic and/or laminate substrate. Alternatively or additionally, the carrier element may, however, also comprise further elements, for example one or more electrodes and/or one or more layers, which may already be applied to the substrate. For example, the p-semiconductor can be applied from the liquid phase to an already partially or completely finished layer structure, in which case, for example, one or more layers may already be applied to a substrate, and then at least one layer of the p-semiconductor is applied. For example, the at least one first electrode, the at least one n-semiconductive metal oxide and preferably the dye may already be applied to a
25 substrate, as described above with regard to the photovoltaic element, before the p-semiconductor is applied from the at least one liquid phase.

30 Application from a liquid phase may generally comprise, for example, a wet chemical processing operation, for example a spin-coating, knife-coating, casting, printing or similar wet chemical processes or combinations of the processes mentioned and/or other processes. For example, it is possible to use printing processes such as inkjet printing, screen printing, offset printing or the like. The application from the liquid phase may especially be followed by drying of the p-semiconductor, for example in order to remove volatile constituents such as solvents of the liquid phase. This drying can be effected, for example, under thermal action, for example at temperatures of 30°C to 150°C. Other
35 configurations are, however, also possible in principle.

The matrix material may especially, as described above, comprise at least one low molecular weight organic p-semiconductor, for example as matrix material. More particularly, it is possible to use one or more of the above-described organic p-

semiconductors. More particularly, the low molecular weight organic p-semiconductor may comprise at least one triphenylamine. The low molecular weight organic p-semiconductor may especially comprise at least one spiro compound, for example one or more of the above-described spiro compounds.

5

The liquid phase may, in addition to the at least one matrix material and the silver in oxidized form, especially the at least one silver(I) salt of the formula $[Ag^+]_m[A^{m-}]$, further comprise one or more additional components which may have different end uses. For example, it is known for stabilization purposes and/or for improvement of the electrical 10 properties to use spiro compounds, for example spiro-MeOTAD, in solution with at least one lithium salt. In general, the liquid phase may accordingly further comprise, for example, at least one metal salt. More particularly, this may be an organometallic salt. A combination of different salts is also possible. More particularly, it is possible to use lithium salts, for example organometallic lithium salts, preferably $LiN(SO_2CF_3)_2$.

15

As described above, the at least one liquid phase may especially comprise at least one solvent. The term "solvent" is used here, in the context of the present invention, irrespective of whether all, several or individual constituents present in the liquid phase are actually present in dissolved form or whether they are present in another form, for example as a suspension, dispersion, emulsion or in some other form. More particularly, the silver in oxidized form, for example the at least one silver(I) salt $[Ag^+]_m[A^{m-}]$ and especially preferably silver bis(trifluoromethylsulfonyl)imide may be present in dissolved form. For example, the at least one matrix material may be present in dissolved or else in dispersed form. The silver in oxidized form, for example the at least one silver(I) salt 20 $[Ag^+]_m[A^{m-}]$ and especially preferably silver bis(trifluoromethylsulfonyl)imide may especially be present in dissolved form, but may also in principle be present in another form, for example in dispersed and/or suspended form.

Particular preference is given to the use of at least one organic solvent. More 30 particularly, it is possible to use one or more of the following solvents: cyclohexanone; chlorobenzene; benzofuran; cyclopentanone.

The proposed process for producing a solid organic p-semiconductor can especially be used to produce the above-described photovoltaic element in one or more of the 35 configurations described. However, other organic components are also producible by means of the process. A combination with other known processes is also conceivable in principle, and so, for example, when a plurality of organic p-semiconductors are provided, one or more of these p-semiconductors are producible by means of the

proposed process according to the invention, and one or more of the conventional p-semiconductors by means of other processes.

A particular advantage of the proposed process for producing the solid organic p-semiconductor is that – in contrast to many processes known from the prior art – storage under air is not necessarily required. For instance, the process may especially be performed at least partly in a low-oxygen atmosphere. In the context of the present invention, an organic component is generally understood to mean a component which has one or more organic elements, for example one or more organic layers. It is possible to use entirely organic components, for example components in which the layer structure – optionally with the exception of the electrodes – comprises only organic layers. However, it is also possible to produce hybrid components, for example components which comprise, as well as one or more organic layers, one or more inorganic layers. When the process proposed is used to produce the solid organic p-semiconductor in a multistep production process, it is possible to perform one, more than one or all of the process steps for production of the organic component in a low-oxygen atmosphere. More particularly, the process step of production of the solid organic p-semiconductor can be performed in the low-oxygen atmosphere, in contrast to the above-described known processes. More particularly, the application of the liquid phase to the carrier element can thus be performed in the low-oxygen atmosphere. A low-oxygen atmosphere is generally understood to mean an atmosphere which has a reduced oxygen content compared to the ambient air. For example, the low-oxygen atmosphere may have an oxygen content of less than 1000 ppm, preferably of less than 500 ppm and more preferably of less than 100 ppm, for example 50 ppm or less. It is also possible to perform further processing of the organic component, for example of the dye solar cell, under such a low-oxygen atmosphere. For example, at least after the application of the solid p-semiconductor by means of the process proposed, the low-oxygen atmosphere cannot be interrupted again until after the encapsulation. Complete processing of the entire component in the low-oxygen atmosphere is also possible, without any adverse effect on the electrical properties of the component. Particular preference is given to a low-oxygen atmosphere in the form of an inert gas, for example a nitrogen atmosphere and/or an argon atmosphere. Mixed gases are also usable.

As detailed above, in a third aspect of the present invention, a process is proposed for producing a photovoltaic element. This may especially be a photovoltaic element according to one or more of the above-described configurations, for example a dye solar cell. The proposed process for producing the photovoltaic element may especially be performed using the above-described process for producing a solid organic p-semiconductor, in which case the process for producing the solid organic p-

semiconductor can be used once or more than once in the context of the proposed process for producing the photovoltaic element. Use of other processes is, however, also possible in principle.

5 The process proposed preferably has the process steps described hereinafter, which can preferably, but not necessarily, be performed in the sequence described. Individual or several process steps can also be performed overlapping in time and/or in parallel. In addition, the performance of additional process steps which are not described is possible. In the process proposed, at least one first electrode, at least one n-
10 semiconductive metal oxide, at least one dye which absorbs electromagnetic radiation, at least one solid organic p-semiconductor and at least one second electrode are provided. This provision can be effected, for example, in the sequence mentioned. More particularly, the provision can be effected by producing a layer structure, for example according to the above description. This layer structure can, for example, be built up
15 successively on one or more substrates. In this case, it is also possible to combine one or more of the elements mentioned to give a combined layer, for example the n-semiconductive metal oxide and the dye.

In the process proposed, the p-semiconductor is configured such that it comprises silver in oxidized form, for example the at least one silver(I) salt $[Ag^+]_m[A^{m-}]$ and especially preferably silver bis(trifluoromethylsulfonyl)imide. The p-semiconductor may especially comprise at least one organic matrix material which is doped by the silver in oxidized form, for example the at least one silver(I) salt $[Ag^+]_m[A^{m-}]$ and especially preferably silver bis(trifluoromethylsulfonyl)imide. For possible configurations of the organic matrix material and/or of the silver in oxidized form, for example the at least one silver(I) salt $[Ag^+]_m[A^{m-}]$ and especially preferably silver bis(trifluoromethylsulfonyl)imide, reference
25 may be made to the description above and below.

The p-semiconductor can especially be produced by a process in which a wet chemical processing operation is used, for example according to the above description of the process for producing the solid organic p-semiconductor. In this wet chemical processing operation, at least one p-conductive organic matrix material and the silver in oxidized form, for example the at least one silver(I) salt $[Ag^+]_m[A^{m-}]$ and especially preferably silver bis(trifluoromethylsulfonyl)imide, as a p-dopant can be applied together to at least one carrier element from at least one liquid phase.
35

Hereinafter, further optionally implementable configurations of the photovoltaic element and of the processes are described, which are particularly preferred in the context of the invention. However, other configurations are also possible in principle.

The photovoltaic element may especially comprise a layer structure, which may be applied, for example, to a substrate. In this case, for example, the first electrode or the second electrode may face the substrate. At least one of the electrodes should be

5 transparent. A " transparent" electrode in this context should especially be understood to mean that, within the visible spectral range and/or in the range of the solar spectrum (approx. 300 nm to 2000 nm), transmission of at least 50% exists, preferably of at least 80%. When the substrate is a transparent substrate, especially the electrode facing the substrate should be transparent.

10 The substrate may be or comprise, for example, a glass substrate and/or a plastic substrate. However, other materials, including a combination of different materials, are also usable in principle, for example laminates. The constituents of the photovoltaic element may be applied to the substrate directly or indirectly as layers. In the context of 15 the present invention, the terms " carrier element" , " carrier" and " substrate" are used at least substantially synonymously. When a carrier element is being discussed, however, this if anything emphasizes the possibility that a layer is being applied indirectly to the substrate, such that at least one further element, especially at least one further layer, may be present between the layer to be applied and the actual substrate.

20 However, direct application is also possible.

The photovoltaic element may especially be a dye solar cell. Accordingly, the photovoltaic element is also referred to hereinafter in general terms as " cell" , without this imposing any restriction to a particular layer structure. A cell may especially 25 comprise the at least one first electrode, the n-conductive metal oxide, the dye, the p-semiconductor and the second electrode. The n-conductive metal oxide, the dye and the p-semiconductor can also be referred to as functional layers, which may be embedded between the electrodes. In addition, the cell may comprise one or more further layers which may, for example, likewise be assigned to the functional layers. One or more cells 30 may be applied directly or indirectly to a substrate. The photovoltaic element may especially comprise one cell or else a plurality of cells. More particularly, a single-cell structure may be selected, or else a multicell structure, for example a tandem cell structure, with a plurality of cells arranged in parallel and/or one on top of another on the substrate.

35 More particularly, the photovoltaic element according to the present invention may be configured in one or more of the ways which follow. The configurations of the elements of the photovoltaic element can also be combined in virtually any way.

First electrode and n-semiconductive metal oxide

The n-semiconductive metal oxide used in the dye solar cell may be a single metal oxide or a mixture of different oxides. It is also possible to use mixed oxides. The n-semiconductive metal oxide may especially be porous and/or be used in the form of a nanoparticulate oxide, nanoparticles in this context being understood to mean particles which have an average particle size of less than 0.1 micrometer. A nanoparticulate oxide is typically applied to a conductive substrate (i.e. a carrier with a conductive layer as the first electrode) by a sintering process as a thin porous film with large surface area.

10 The substrate may be rigid or else flexible. Suitable substrates (also referred to hereinafter as carriers) are, as well as metal foils, in particular plastic sheets or films and especially glass sheets or glass films. Particularly suitable electrode materials, especially for the first electrode according to the above-described, preferred structure, are 15 conductive materials, for example transparent conductive oxides (TCOs), for example fluorine- and/or indium-doped tin oxide (FTO or ITO) and/or aluminum-doped zinc oxide (AZO), carbon nanotubes or metal films. Alternatively or additionally, it would, however, also be possible to use thin metal films which still have a sufficient transparency. The substrate can be covered or coated with these conductive materials. Since generally only 20 a single substrate is required in the structure proposed, the formation of flexible cells is also possible. This enables a multitude of end uses which would be achievable only with difficulty, if at all, with rigid substrates, for example use in bank cards, garments, etc.

25 The first electrode, especially the TCO layer, may additionally be covered or coated with a solid metal oxide buffer layer (for example of thickness 10 to 200 nm), in order to prevent direct contact of the p-semiconductor with the TCO layer (see Peng *et al.*, Coord. Chem. Rev. 248, 1479 (2004)). The inventive use of solid p-semiconductive electrolytes, in the case of which contact of the electrolyte with the first electrode is 30 greatly reduced compared to liquid or gel-form electrolytes, however, makes this buffer layer unnecessary in many cases, such that it is possible in many cases to dispense with this layer, which also has a current-limiting effect and can also worsen the contact of the n-semiconductive metal oxide with the first electrode. This enhances the efficiency of the components. On the other hand, such a buffer layer can in turn be utilized in a controlled manner in order to match the current component of the dye solar cell to the current 35 component of the organic solar cell. In addition, in the case of cells in which the buffer layer has been dispensed with, especially in solid cells, problems frequently occur with unwanted recombinations of charge carriers. In this respect, buffer layers are advantageous in many cases specifically in solid cells.

As is well known, thin layers or films of metal oxides are generally inexpensive solid semiconductor materials (n-semiconductors), but the absorption thereof, due to large bandgaps, is typically not within the visible region of the electromagnetic spectrum, but rather usually in the ultraviolet spectral region. For use in solar cells, the metal oxides therefore generally, as is the case in the dye solar cells, have to be combined with a dye as a photosensitizer, which absorbs in the wavelength range of sunlight, i.e. at 300 to 2000 nm, and, in the electronically excited state, injects electrons into the conduction band of the semiconductor. With the aid of a solid p-semiconductor used additionally in the cell as an electrolyte, which is in turn reduced at the counterelectrode (or, in the case of a tandem solar cell, at the transition to the second subcell), electrons can be recycled to the sensitizer, such that it is regenerated.

Of particular interest for use in solar cells are the semiconductors zinc oxide, tin dioxide, titanium dioxide or mixtures of these metal oxides. The metal oxides can be used in the form of nanocrystalline porous layers. These layers have a large surface area which is coated with the dye as a sensitizer, such that a high absorption of sunlight is achieved. Metal oxide layers which are structured, for example nanorods, give advantages such as higher electron mobilities or improved pore filling by the dye.

20 The metal oxide semiconductors can be used alone or in the form of mixtures. It is also possible to coat a metal oxide with one or more other metal oxides. In addition, the metal oxides may also be applied as a coating to another semiconductor, for example GaP, ZnP or ZnS.

25 Particularly preferred semiconductors are zinc oxide and titanium dioxide in the anatase polymorph, which is preferably used in nanocrystalline form.

In addition, the sensitizers can advantageously be combined with all n-semiconductors which typically find use in these solar cells. Preferred examples include metal oxides used in ceramics, such as titanium dioxide, zinc oxide, tin(IV) oxide, tungsten(VI) oxide, tantalum(V) oxide, niobium(V) oxide, cesium oxide, strontium titanate, zinc stannate, complex oxides of the perovskite type, for example barium titanate, and binary and ternary iron oxides, which may also be present in nanocrystalline or amorphous form.

35 Due to the strong absorption that customary organic dyes and phthalocyanines and porphyrins have, even thin layers or films of the n-semiconductive metal oxide are sufficient to absorb the required amount of dye. Thin metal oxide films in turn have the advantage that the probability of unwanted recombination processes falls and that the inner resistance of the dye subcell is reduced. For the n-semiconductive metal oxide, it is

possible with preference to use layer thicknesses of 100 nm up to 20 micrometers, more preferably in the range between 500 nm and approx. 3 micrometers.

Dye

5 In the context of the present invention, as usual for DSCs, the terms "dye", "sensitizer dye" and "sensitizer" are used essentially synonymously without any restriction of possible configurations. Numerous dyes which are usable in the context of the present invention are known from the prior art, and so, for possible material examples, reference may also be made to the above description of the prior art regarding dye solar cells. All dyes listed and claimed may in principle also be present as pigments. Dye-sensitized solar cells based on titanium dioxide as a semiconductor material are described, for example, in US-A-4 927 721, Nature 353, p. 737-740 (1991) and US-A-5 350 644, and also Nature 395, p. 583-585 (1998) and EP-A-1 176 646. The dyes described in these documents can in principle also be used advantageously in the context of the present invention. These dye solar cells preferably comprise monomolecular films of transition metal complexes, especially ruthenium complexes, which are bonded to the titanium dioxide layer via acid groups as sensitizers.

20 Not least for reasons of cost, sensitizers which have been proposed repeatedly include metal-free organic dyes, which are likewise also usable in the context of the present invention. High efficiencies of more than 4%, especially in solid dye solar cells, can be achieved, for example, with indoline dyes (see, for example, Schmidt-Mende *et al.*, Adv. Mater. 2005, 17, 813). US-A-6 359 211 describes the use, also implementable in the context of the present invention, of cyanine, oxazine, thiazine and acridine dyes which have carboxyl groups bonded via an alkylene radical for fixing to the titanium dioxide semiconductor.

25 Organic dyes now achieve efficiencies of almost 12.1% in liquid cells (see, for example, P. Wang *et al.*, ACS. Nano 2010). Pyridinium-containing dyes have also been reported, can be used in the context of the present invention and exhibit promising efficiencies.

30 Particularly preferred sensitizer dyes in the dye solar cell proposed are the perylene derivatives, terrylene derivatives and quaterrylene derivatives described in DE 10 2005 053 995 A1 or WO 2007/054470 A1. The use of these dyes leads to photovoltaic elements with high efficiencies and simultaneously high stabilities.

The rylene exhibit strong absorption in the wavelength range of sunlight and can, depending on the length of the conjugated system, cover a range from about 400 nm

(perylene derivatives I from DE 10 2005 053 995 A1) up to about 900 nm (quatterylene derivatives I from DE 10 2005 053 995 A1). Rylene derivatives I based on terrylene absorb, according to the composition thereof, in the solid state adsorbed onto titanium dioxide, within a range from about 400 to 800 nm. In order to achieve very substantial utilization of the incident sunlight from the visible into the near infrared region, it is advantageous to use mixtures of different rylene derivatives I. Occasionally, it may also be advisable also to use different rylene homologs.

The rylene derivatives I can be fixed easily and in a permanent manner to the n-semiconductive metal oxide film. The bonding is effected via the anhydride function (x1) or the carboxyl groups – COOH or – COO- formed in situ, or via the acid groups A present in the imide or condensate radicals ((x2) or (x3)). The rylene derivatives I described in DE 10 2005 053 995 A1 have good suitability for use in dye-sensitized solar cells in the context of the present invention.

It is particularly preferred when the dyes, at one end of the molecule, have an anchor group which enables the fixing thereof to the n-semiconductor film. At the other end of the molecule, the dyes preferably comprise electron donors Y which facilitate the regeneration of the dye after the electron has been released to the n-semiconductor, and also prevents recombination with electrons already released to the semiconductor.

For further details regarding the possible selection of a suitable dye, it is possible, for example, again to refer to DE 10 2005 053 995 A1. For the tandem cells described in the present document, it is possible especially to use ruthenium complexes, porphyrins, other organic sensitizers, and preferably rylenes.

The dyes can be fixed onto or into the n-semiconductive metal oxide films in a simple manner. For example, the n-semiconductive metal oxide films can be contacted in the freshly sintered (still warm) state over a sufficient period (for example about 0.5 to 24 h) with a solution or suspension of the dye in a suitable organic solvent. This can be accomplished, for example, by immersing the metal oxide-coated substrate into the solution of the dye.

If combinations of different dyes are to be used, they may, for example, be applied successively from one or more solutions or suspensions which comprise one or more of the dyes. It is also possible to use two dyes which are separated by a layer of, for example, CuSCN (on this subject see, for example, Tennakone, K.J., *Phys. Chem. B.* 2003, 107, 13758). The most convenient method can be determined comparatively easily in the individual case.

In the selection of the dye and of the size of the oxide particles of the n-semiconductive metal oxide, the solar cell should be configured such that a maximum amount of light is absorbed. The oxide layers should be structured such that the solid p-semiconductor can

5 efficiently fill the pores. For instance, smaller particles have greater surface areas and are therefore capable of adsorbing a greater amount of dyes. On the other hand, larger particles generally have larger pores which enable better penetration through the p-conductor.

10 As described above, the concept proposed comprises the use of one or more solid p-semiconductors. In order to prevent recombination of the electrons in the n-semiconductive metal oxide with the solid p-conductor, it is possible to use, between the n-semiconductive metal oxide and the p-semiconductor, at least one passivating layer which has a passivating material. This layer should be very thin and should as far as

15 possible cover only the as yet uncovered sites of the n-semiconductive metal oxide. The passivation material may, under some circumstances, also be applied to the metal oxide before the dye. Preferred passivation materials are especially one or more of the following substances: Al_2O_3 ; silanes, for example CH_3SiCl_3 ; Al^{3+} ; 4-tert-butylpyridine (TBP); MgO ; GBA (4-guanidinobutyric acid) and similar derivatives; alkyl acids; 20 hexadecylmalonic acid (HDMA).

p-semiconductor

As described above, in the context of the photovoltaic element proposed here, one or 25 more solid organic p-semiconductors are used – alone or else in combination with one or more further p-semiconductors which are organic or inorganic in nature. The at least one solid organic p-semiconductor comprises, as described above, at least silver in oxidized form. In the context of the present invention, a p-semiconductor is generally understood to mean a material, especially an organic material, which is capable of 30 conducting holes. More particularly, it may be an organic material with an extensive π -electron system which can be oxidized stably at least once, for example to form what is called a free-radical cation. For example, the p-semiconductor may comprise at least one organic matrix material which has the properties mentioned. More particularly, the p-semiconductor may be p-doped by the silver(I). This means that any p-semiconductive 35 property present in any case in the p-semiconductor or in the matrix material is enhanced or even actually created by the doping with silver(I). More particularly, the doping can increase a charge carrier density, especially a hole density. Alternatively or additionally, a mobility of the charge carriers, especially of the holes, can also be influenced by the doping, especially increased.

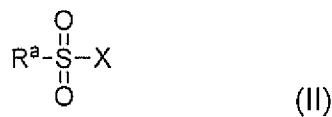
More particularly, the doped p-semiconductor, as described above, may be producible or have been produced by applying at least one p-conductive organic material and silver in oxidized form to at least one carrier element, wherein the silver in oxidized form is 5 preferably applied to at least one carrier element in the form of at least one silver(I) salt $[Ag^+]_m[A^{m-}]$ where A^{m-} is the anion of an organic or inorganic acid, and m is an integer in the range from 1 to 3, preferably where m is 1.

With regard to the integer m, m is preferably 1 or 2, very preferably 1. Accordingly, for 10 production of the p-semiconductor, it is very preferable to use a salt of the formula Ag^+A^- .

With regard to A^{m-} , this is preferably an anion of an organic or inorganic acid.

In a preferred embodiment, A^{m-} is an anion of an organic acid, the organic acid preferably 15 comprising at least one fluorine group or cyano group (-CN), more preferably at least one fluorine group. Preferably, $[A^{m-}]$ is the anion of an organic carboxylic acid, sulfonic acid, phosphonic acid or sulfonimide each preferably comprising at least one fluorine group or cyano group.

20 Preferably, the present invention relates to a photovoltaic element, as described above, where $[A^{m-}]$ has a structure of the formula (II)



25 where R^a is a fluorine group -F or an alkyl radical, cycloalkyl radical, aryl radical or heteroaryl radical each substituted by at least one fluorine group or cyano group,

and where X is - O- or - N—Rb,

30 and where R^b comprises a fluorine group - F or a cyano group,

and where R^b further comprises a group of the formula -S(O)₂-.

35 The term " cycloalkyl radical" or " cycloalkyl group" as used in the context of the present invention relates to cyclic, optionally substituted alkyl groups, preferably 5- or 6-membered rings or multicyclic rings which further preferably have 5 to 20 carbon atoms.

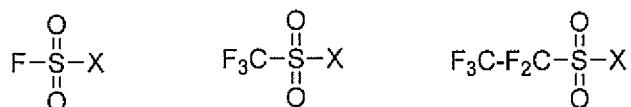
R^a radical:

In a preferred embodiment of the invention, R^a is -F or an alkyl radical substituted at least by one fluorine group or one cyano group, preferably by at least one fluorine group, very preferably a methyl group, ethyl group or propyl group substituted by at least one fluorine group or a cyano group, preferably a fluorine group. In addition to the fluorine group or the cyano group, the alkyl radical may comprise at least one further substituent. Preferably, R^a comprises at least 3 fluorine substituents or one cyano group, more preferably at least 3 fluorine substituents.

10 R^a is especially selected from the group consisting of -F, -CF₃, -CF₂-CF₃ and -CH₂-CN, further preferably selected from the group consisting of -F, -CF₃ and -CF₂-CF₃.

Accordingly, the present invention also relates to a photovoltaic element, as described above, where [A^{m-}] has a structure selected from the following formulae:

15

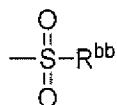


and where X is -O⁻ or -N—Rb. More preferably, R^a is -CF₃.

20 R^b radical:

As described above, R^b is a group comprising a fluorine group -F or a cyano group, where R^b additionally comprises a group of the formula -S(O)₂⁻. Preferably, R^b comprises at least one alkyl, cycloalkyl, aryl or heteroaryl radical, where the alkyl, 25 cycloalkyl, aryl or heteroaryl radical is in each case substituted by at least one fluorine group -F or a cyano group, preferably by at least one fluorine group, and where R^b additionally comprises a group of the formula -S(O)₂⁻.

30 Preferably, R^b has a structure of the following formula:

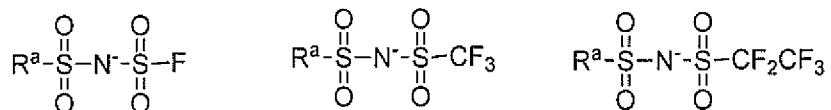


where R^{bb} is -F or an alkyl group substituted by at least one fluorine group or a cyano group, preferably at least one fluorine group, very preferably a methyl group, ethyl group or propyl group substituted by at least one fluorine group. In addition to the fluorine group and/or cyano group, the alkyl radical may comprise at least one further substituent. Preferably, R^{bb} comprises at least 3 fluorine substituents.

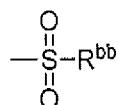
R^{bb} is especially selected from the group consisting of -F, -CF₃, -CF₂-CF₃ and -S(O)₂-CH₂-CN, especially selected from the group consisting of -F, -CF₃ and -CF₂-CF₃.

5 Accordingly, the present invention also relates to a photovoltaic element as described above, where X is -N-Rb, and where R^b is selected from the group consisting of -S(O)₂-F, -S(O)₂-CF₃, -S(O)₂-CF₂-CF₃ and -S(O)₂-CH₂-CN, especially selected from the group consisting of -S(O)₂-F, -S(O)₂-CF₃, and -S(O)₂-CF₂-CF₃.

10 [A^{m-}] accordingly most preferably has one of the following structures:



15 where R^a is especially selected from the group consisting of -F, -CF₃ and -CF₂-CF₃. Preferably, in the case that X is -N-Rb and Rb has the structure



20 R^a and R^{bb} are the same; [A^{m-}] is accordingly more preferably a symmetric sulfonylimide. In a preferred embodiment, [A^{m-}] is accordingly selected from bis(trifluoromethylsulfonyl)imide (TFSI⁻), bis(trifluoroethylsulfonyl)imide, and bis(fluorosulfonyl)imide.

25 In an alternative embodiment, the present invention relates to a photovoltaic element as described above where [A^{m-}] is a trifluoroacetate group.

30 In a further preferred embodiment, [A^{m-}] is the anion of an inorganic acid. In this case, [A^{m-}] is preferably -NO₃⁻ (nitrate). Accordingly, the present invention also relates to a photovoltaic element which, as described above, is producible or has been produced by introducing, especially mixing and/or dissolving, at least one silver(I) salt [Ag⁺]_m[A^{m-}] into at least one organic matrix material (128), where [A^{m-}] is an -NO₃⁻ group and where m = 1.

35 Accordingly, the present invention also relates to a photovoltaic element as described above, where [A^{m-}] is selected from the group consisting of bis(trifluoromethylsulfonyl)imide (TFSI⁻), bis(trifluoroethylsulfonyl)imide,

bis(fluorosulfonyl)imide, trifluoromethylsulfonate, preferably where $[A^m]$ is bis(trifluoromethylsulfonyl)imide (TFSI $^-$).

5 Solid p-semiconductors doped with at least silver in oxidized form, for example the at least one silver(I) salt $[Ag^+]_m[A^m]$ and especially preferably silver bis(trifluoromethylsulfonyl)imide, can be used in the inventive photovoltaic elements even without any great increase in the cell resistance, especially when the dyes absorb strongly and therefore require only thin n-semiconductor layers. More particularly, the p-semiconductor should essentially have a continuous, impervious layer, in order that 10 unwanted recombination reactions which could result from contact between the n-semiconductive metal oxide (especially in nanoporous form) with the second electrode and/or further elements of the photovoltaic element are reduced.

15 The silver in oxidized form, for example the at least one silver(I) salt $[Ag^+]_m[A^m]$ and especially preferably silver bis(trifluoromethylsulfonyl)imide, can especially be applied to the carrier element, together with the matrix material from the liquid phase. For example, the silver in oxidized form, for example the at least one silver(I) salt $[Ag^+]_m[A^m]$ and especially preferably silver bis(trifluoromethylsulfonyl)imide, can be processed as a 20 solution, dispersion or suspension, in combination with a p-semiconductive matrix material. Optionally, at least one organic salt can be added to this at least one liquid phase (though it is also possible for several liquid phases to be present), for example for stabilization purposes and/or for improvement of the electrical properties.

25 A significant parameter influencing the selection of the p-semiconductor is the hole mobility, since this partly determines the hole diffusion length (cf. Kumara, G., Langmuir, 2002, 18, 10493-10495). A comparison of charge carrier mobilities in different spiro compounds can be found, for example, in T. Saragi, Adv. Funct. Mater. 2006, 16, 966-974.

30 Preferably, in the context of the present invention, organic semiconductors are used (i.e. low molecular weight, oligomeric or polymeric semiconductors or mixtures of such semiconductors). Particular preference is given to p-semiconductors which can be processed from a liquid phase. Examples here are p-semiconductors based on polymers such as polythiophene and polyarylamines, or on amorphous, reversibly oxidizable, 35 nonpolymeric organic compounds, such as the spirobifluorenes mentioned at the outset (cf., for example, US 2006/0049397 and the spiro compounds disclosed therein as p-semiconductors, which are also usable in the context of the present invention). Preference is given to using low molecular weight organic semiconductors. The solid p-semiconductors can be used in doped form with silver in oxidized form, for example the

at least one silver(I) salt $[Ag^+]_m[A^{m-}]$ and especially preferably silver bis(trifluoromethylsulfonyl)imide, as a dopant.

5 In addition, reference may also be made to the remarks regarding the p-semiconductive materials and dopants from the description of the prior art. For the other possible elements and the possible structure of the dye solar cell, reference may also be made substantially to the above description.

Second electrode

10 The second electrode may be a bottom electrode facing the substrate or else a top electrode facing away from the substrate. The second electrodes which can be used are especially metal electrodes which may have one or more metals in pure form or as a mixture/alloy, such as especially aluminum or silver. The use of inorganic/organic mixed 15 electrodes or multilayer electrodes is also possible, for example the use of LiF/Al electrodes.

20 In addition, it is also possible to use electrode designs in which the quantum efficiency of the components is increased by virtue of the photons being forced, by means of appropriate reflections, to pass through the absorbing layers at least twice.

Such layer structures are also referred to as " concentrators" and are likewise described, for example, in WO 02/101838 (especially p. 23-24).

25 Brief description of the figures

Further details and features of the invention are evident from the description of preferred 30 embodiments which follows in conjunction with the dependent claims. In this context, the particular features may be implemented alone or with several in combination. The invention is not restricted to the working examples. The working examples are shown schematically in the figures. Identical reference numerals in the individual figures refer to identical elements or elements with identical function, or elements which correspond to one another with regard to their functions.

35 The individual figures show:

figure 1 a schematic layer structure of an inventive organic photovoltaic element in a sectional diagram in side view;

figure 2 a schematic arrangement of the energy levels in the layer structure according to figure 1;

5 figure 3 current-voltage characteristic of a comparative sample without silver in oxidized form, measured 2 days after production;

figure 4 current-voltage characteristics with Ag-TFSI doping.

Working examples

10 Figure 1 shows, in a highly schematic sectional diagram, a photovoltaic element 110 which, in this working example, is a dye solar cell 112. The photovoltaic element 110 according to the schematic layer structure in figure 1 can be configured in accordance with the invention. The comparative sample according to the prior art may in principle 15 also correspond to the structure shown in figure 1, and differ therefrom, for example, merely with regard to the solid organic p-semiconductor. It is pointed out that the present invention, however, is also usable in other layer structures and/or in other constructions.

20 The photovoltaic element 110 comprises a substrate 114, for example a glass substrate. Other substrates are also usable, as described above. Applied to this substrate 114 is a first electrode 116, which is also referred to as a working electrode and which preferably, as described above, is transparent. Applied to this first electrode 116 in turn is a blocking layer 118 of an optional metal oxide, which is preferably nonporous and/or nonparticulate. Applied to this in turn is an n-semiconductive metal oxide 120 which has 25 been sensitized with a dye 122.

30 The substrate 114 and the layers 116 to 120 applied thereto form a carrier element 124 for at least one layer, applied thereto, of a solid organic p-semiconductor 126, which in turn may comprise especially at least one p-semiconductive organic matrix material 128 and at least one silver in oxidized form 130, for example the at least one silver(I) salt $[Ag^+]_m[A^m]$ and especially preferably silver bis(trifluoromethylsulfonyl)imide. Applied to this p-semiconductor 126 is a second electrode 132, which is also referred to as the 35 counterelectrode. The layers shown in figure 1 together form a layer structure 134 which has been shielded from a surrounding atmosphere by an encapsulation 136, for example in order to completely or partially protect the layer structure 134 from oxygen and/or moisture. One or both of the electrodes 116, 132 may, as indicated in figure 1 with reference to the first electrode 116, be conducted out of the encapsulation 136, in order to be able to provide one or more contact connection areas outside the encapsulation 136.

Figure 2 shows, by way of example, in a highly schematic manner, an energy level diagram of the photovoltaic element 110, for example according to figure 1. What are shown are the Fermi levels 138 of the first electrode 116 and of the second electrode 5 132, and the HOMOs (highest occupied molecular orbitals) 140 and the LUMOs (lowest unoccupied molecular orbitals) of the layers 118/120 (which may comprise the same material, for example TiO_2) of the dye (shown by way of example with a HOMO level of 5.7 eV) and of the p-semiconductor 126 (also referred to as HTL, hole transport layer). The materials specified by way of example for the first electrode 116 and the second 10 electrode 132 are FTO (fluorine-doped tin oxide) and silver.

The photovoltaic elements may additionally optionally comprise further elements. By means of photovoltaic elements 110 with or without encapsulation 136, the working examples described hereinafter were implemented, on the basis of which the effect of 15 the present invention and especially of the p-doping of the p-semiconductor 126 by means of silver in oxidized form 130 can be demonstrated.

Comparative sample

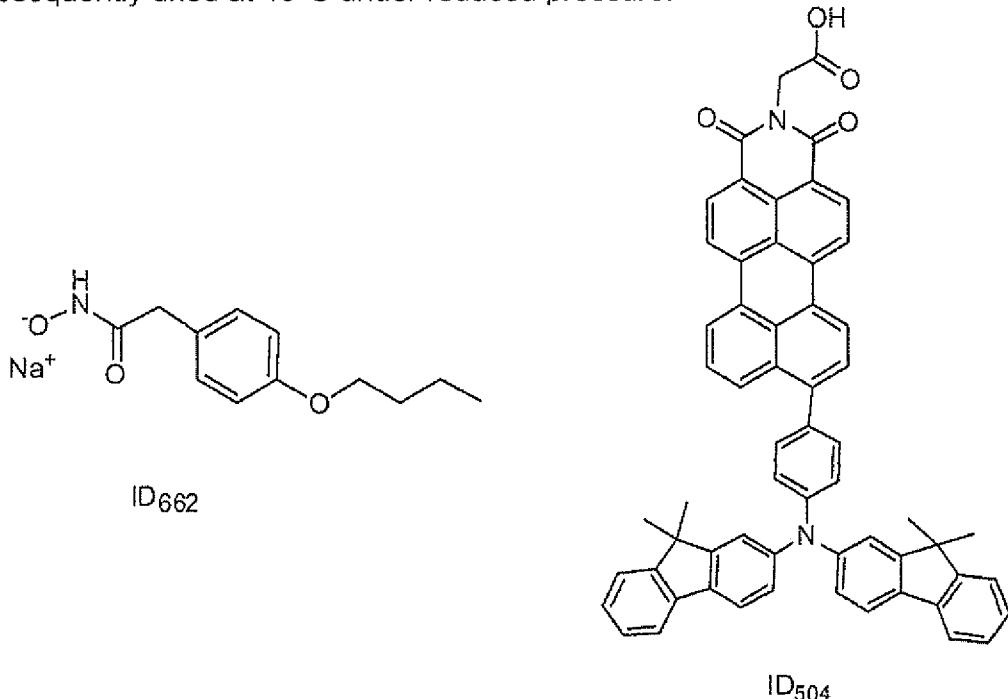
20 As a comparative sample of a photovoltaic element, a dye solar cell with a solid p-semiconductor without doping with silver in oxidized form was produced, as known in principle from the prior art.

25 As the base material and substrate, glass plates which had been coated with fluorine-doped tin oxide (FTO) as the first electrode (working electrode) and were of dimensions 25 mm \times 25 mm \times 3 mm (Hartford Glass) were used, which were treated successively in an ultrasound bath with glass cleaner (RBS 35), demineralized water and acetone, for 5 min in each case, then boiled in isopropanol for 10 min and dried in a nitrogen stream.

30 To produce an optional solid TiO_2 buffer layer, a spray pyrolysis process was used. Thereon, as an n-semiconductive metal oxide, a TiO_2 paste (Dyesol) which comprises TiO_2 particles with a diameter of 25 nm in a terpineol/ethylcellulose dispersion was spun on with a spin-coater at 4500 rpm and dried at 90°C for 30 min. After heating to 450°C for 45 min and a sintering step at 450°C for 30 minutes, a TiO_2 layer thickness of 35 approximately 1.8 μm was obtained.

After removal from the drying cabinet, the sample was cooled to 80°C and immersed into a 5 mM solution of an additive ID662 (obtainable according to example H, for example) for 12 h and subsequently into a 0.5 mM solution of a dye in dichloromethane for 1 h.

The dye used was the dye ID504 (obtainable according to example G, for example). After removal from the solution, the sample was subsequently rinsed with the same solvent and dried in a nitrogen stream. The samples obtained in this way were subsequently dried at 40°C under reduced pressure.



5

Next, a p-semiconductor solution was spun on. For this purpose, a solution of 0.12 M spiro-MeOTAD (Merck) and 20 mM LiN(SO₂CF₃)₂ (Aldrich) in chlorobenzene was made up. 125 µl of this solution were applied to the sample and allowed to act for 60 s.

10 Thereafter, the supernatant solution was spun off at 2000 rpm for 30 s and the sample was stored under air in the dark overnight. As stated above, it is suspected that this storage brings about oxygen doping of the p-semiconductor, as a result of which the conductivity of the p-semiconductor is enhanced.

15 Finally, a metal back electrode was applied as a second electrode by thermal metal vaporization under reduced pressure. The metal used was Ag, which was vaporized at a rate of 3 Å/s at a pressure of approx. 2*10⁻⁶ mbar, so as to give a layer thickness of about 200 nm.

20 After the production, the cell was stored under dry air (8% relative air humidity) for 2 days.

To determine the efficiency η , the particular current/voltage characteristic was measured with a source meter model 2400 (Keithley Instruments Inc.) under irradiation with a

xenon solar simulator (LOT-Oriel 300 W AM 1.5) two days after production. The initial measurement was effected with unencapsulated cells. A current-voltage characteristic of the comparative sample measured after two days is shown in figure 3. The comparative sample had the characteristics shown in table 1.

5

	Isc[mA/cm ²]	Voc[mV]	FF[%]	ETA[%]
no Ag-TFSI, t=2 days	9.29	860	55	4.4

Table 1: Characteristics of comparative sample without doping.

The short-circuit current Isc (i.e. the current density at load resistance zero) was 9.29 mA/cm², the open-circuit voltage V_{oc} (i.e. the load at which the current density has 10 fallen to zero) was 860 mV, the fill factor FF was 55% and the efficiency ETA was 4%.

Example 1: Doping with 5 mm AG-TFSI

As the first working example of an inventive photovoltaic element 110, the above-15 described comparative sample was modified by doping the p-semiconductor 126 or the matrix material 128 thereof with silver bis(trifluoromethylsulfonyl)imide (Ag-TFSI). For this purpose, 5 mm silver bis(trifluoromethylsulfonyl)imide (source: Aldrich) in cyclohexanone was added to the p-semiconductor solution of 0.12M spiro-MeOTAD (source: Merck) and 20 mm LiN(BO₂CF₃)₂ (source: Aldrich) in chlorobenzene. This 20 solution was then spun onto the sample as described for the comparative sample.

The metal back electrode as the second electrode 132 was applied immediately thereafter by thermal metal vaporization under reduced pressure. The metal used was Ag, which was vaporized at a rate of 3 Å/s at a pressure of approx. 2*10⁻⁶ mbar so as to 25 form a layer thickness of about 200 nm.

To determine the efficiency η , the particular current/voltage characteristic was measured with a Source Meter Model 2400 (Keithley Instruments Inc.) under irradiation with a xenon solar simulator (LOT-Oriel 300 W AM 1.5) immediately and 2 days after 30 production. The initial measurement was effected with unencapsulated cells.

Current-voltage characteristics with 5 mm silver bis(trifluoromethylsulfonyl)imide are shown in figure 4. The characteristics of the comparative sample and of the sample according to example 1 are shown in table 2.

35

	Isc[mA/cm ²]	Voc[mV]	FF[%]	ETA[%]
no Ag-TFSI, t=0	4.13	760	26	0.8

no Ag-TFSI, t=2 days	9.29	860	55	4.4
with Ag-TFSI, t=0	9.20	800	69	5.1
with Ag-TFSI, t=2 days	9.80	780	66	5.0

Table 2: Comparison of characteristics of an undoped comparative sample and of a sample according to example 1 at different measurement times.

5 Example 2: Variation of the dopant concentration

In order to study the influence of the amount of dopant on the properties of the photovoltaic element 110, variations of example 1 were additionally produced with 1-
10 20 mm silver bis(trifluoromethylsulfonyl)imide. Otherwise, the samples were produced like the sample according to the above-described example 1. The characteristics of these samples, measured after 2 days, are shown in table 3. The illumination in these measurements was in each case again 100 sun, as already in the measurements above.

	Isc[mA/cm ²]	Voc[mV]	FF[%]	ETA[%]
1 mM Ag-TFSI	-10.4	780	53	4.3
3 mM Ag-TFSI	-10.1	780	62	4.8
5 mM Ag-TFSI	-9.8	780	66	5.0
10 mM Ag-TFSI	-9.7	760	69	5.1
20 mM Ag-TFSI	-9.7	800	64	4.9

15 Table 3: Comparison of characteristics of samples according to example 2 with different Ag-TFSI content.

The measurements show that, in terms of efficiency, a maximum of approx. 5.1% occurs at approx. 10 mm Ag-TFSI. Overall, the efficiency between 3 mm and 20 mm, however, follows a comparatively flat profile, which may constitute an advantage in terms of
20 production technology.

Example 3: Variation of the matrix material

In addition, as example 3, the influence of the matrix material 128 on the properties of
25 the photovoltaic elements 110 was studied. For this purpose, samples were produced according to the above-described example 1, except that spiro-MeOTAD as matrix material 128 was replaced by different matrix materials 128 with different concentrations, more particularly by the matrix materials of the ID522, ID322 and ID367 types already mentioned above. To introduce silver 130 in oxidized form, the dopant used was again in
30 each case 10 mm silver bis(trifluoromethylsulfonyl)imide in all samples. The

characteristics of the samples obtained in this way are shown in table 4. The specified concentrations of 160 mg/ml and 200 mg/ml are based on the concentration of the matrix material 128 in the liquid phase. The characteristics were again recorded after 2 days and measured at 100 sun [mW/cm²].

5

p-Conductor	Comment	Isc[mA/cm ²]	Voc[mV]	FF[%]	ETA[%]
ID522	conc. 160mg/ml, 10 mM AgTFSI	-6.22	740	73	3.4
ID522	conc. 200mg/ml, 10 mM AgTFSI	-7.07	740	70	3.7
ID322	conc. 160mg/ml, 10 mM AgTFSI	-1.68	500	40	0.3
ID322	conc. 200mg/ml, 10 mM AgTFSI	-1.49	580	39	0.3
ID367	conc. 160mg/ml, 10 mM AgTFSI	-6.89	760	73	3.8
ID367	conc. 200mg/ml, 10 mM AgTFSI	-7.14	740	71	3.7

Table 4: Comparison of characteristics of samples according to example 4 with different matrix materials.

10

Example 4: Variation of the dopant

In addition, tests in which silver 130 in oxidized form was introduced into the matrix material 128 by means of other dopants were conducted. In addition, silver in Ag-TFSI 15 was replaced by other groups in order to check whether the doping effect and the positive effect thereof on the characteristics of the photovoltaic components 110 is possibly caused by TFSI instead of by the silver 130 in oxidized form.

For this purpose, in example 4, various samples which correspond again to example 1 20 above apart from the dopant were produced. Instead of Ag-TFSI, however, other salts as dopants were each added in an amount of 20 mm. The results are shown in table 5. Silver nitrate was added in solid form to the p-conductor solution.

Dopant	Isc[mA/cm ²]	Voc[mV]	FF[%]	ETA[%]
Ag nitrate	-9.8	800	66	5.1

Ag triflate	-4.4	920	43	1.8
Ag trifluoroacetate	-1.2	640	35	0.3
1-ethyl-3-methyl-TFSI	-1.9	1000	39	0.7
1-butyl-3-methyl-TFSI	-1.2	1000	26	0.3
Na triflate	-1.6	1000	29	0.5

Table 5: Comparison of characteristics of samples according to example 5 with different dopants.

5 The results show that TFSI in general leads to high efficiencies only as an anion in a silver salt. In addition to Ag-TFSI, however, other silver salts also exhibit comparatively high efficiencies, especially silver nitrate and silver triflate. In general, it is thus possible to use compounds, especially salts, containing silver in oxidized form as a dopant, especially silver(I) salts of the formula $[Ag^+]_m[A^m]$, more preferably Ag-TFSI, silver nitrate and silver triflate.

10

Finally, synthesis examples of low molecular weight organic p-semiconductors are also listed hereinafter, which are usable individually or in combination in the context of the present invention and which can, for example, satisfy the formula I given above.

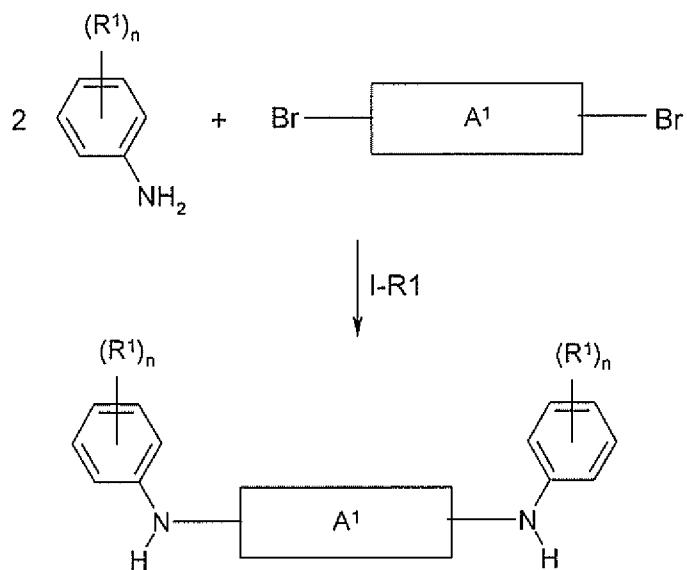
15

Synthesis examples:

(A) General synthesis schemes for preparation of compounds of the formula I:

20 (a) *Synthesis route I:*

(a1) Synthesis step I-R1:



The synthesis in synthesis step I-R1 was based on the references cited below:

5 a) Liu, Yunqi; Ma, Hong; Jen, Alex K-Y.; CHCOFS; Chem. Commun.; 24; 1998; 2747-
2748,

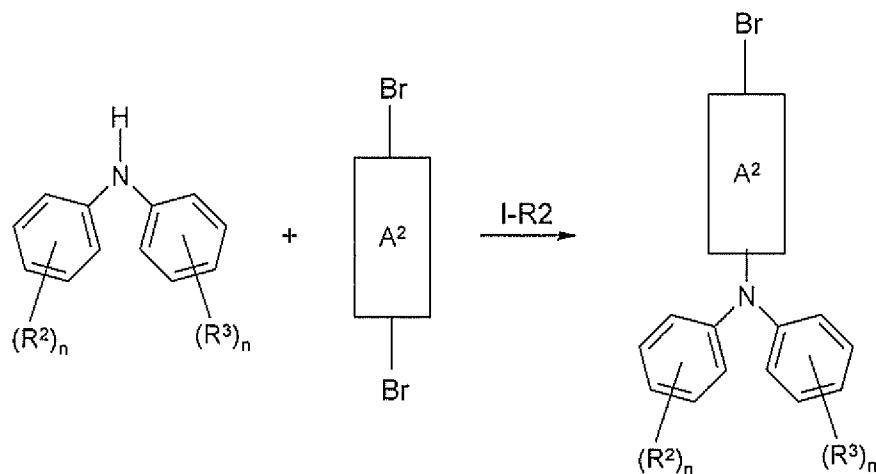
10 b) Goodson, Felix E.; Hauck, Sheila; Hartwig, John F.; J. Am. Chem. Soc.; 121; 33;
1999; 7527 – 7539,

c) Shen, Jiun Yi; Lee, Chung Ying; Huang, Tai-Hsiang; Lin, Jiann T.; Tao, Yu-Tai; Chien,
Chin-Hsiung; Tsai, Chiitang; J. Mater. Chem.; 15; 25; 2005; 2455 – 2463,

15 d) Huang, Ping-Hsin; Shen, Jiun-Yi; Pu, Shin-Chien; Wen, Yuh-Sheng; Lin, Jiann T.;
Chou, Pi-Tai; Yeh, Ming-Chang P.; J. Mater. Chem.; 16; 9; 2006; 850 – 857,

e) Hirata, Narukuni; Kroeze, Jessica E.; Park, Taiho; Jones, David; Haque, Saif A.;
Holmes, Andrew B.; Durrant, James R.; Chem. Commun.; 5; 2006; 535 - 537.

20 (a2) *Synthesis step I-R2:*



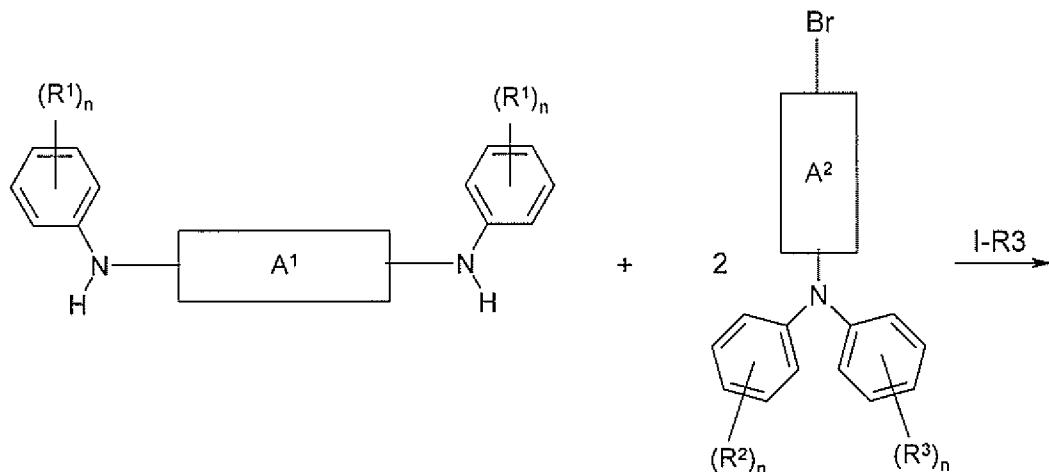
The synthesis in synthesis step I-R2 was based on the references cited below:

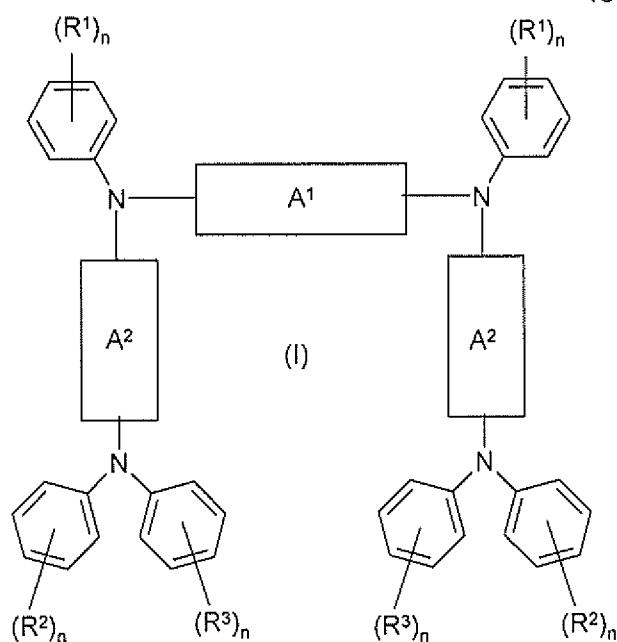
a) Huang, Qinglan; Evmenenko, Guennadi; Dutta, Pulak; Marks, Tobin J.; J. Am. Chem. Soc.; 125; 48; 2003; 14704 – 14705,

b) Bacher, Erwin; Bayerl, Michael; Rudati, Paula; Reckefuss, Nina; Mueller, C. David; Meerholz, Klaus; Nuyken, Oskar; Macromolecules; EN; 38; 5; 2005; 1640 – 1647,

c) Li, Zhong Hui; Wong, Man Shing; Tao, Ye; D'Iorio, Marie; J. Org. Chem.; EN; 69; 3; 2004; 921 - 927.

(a3) *Synthesis step I-R3:*





The synthesis in synthesis step I-R3 was based on the reference cited below:

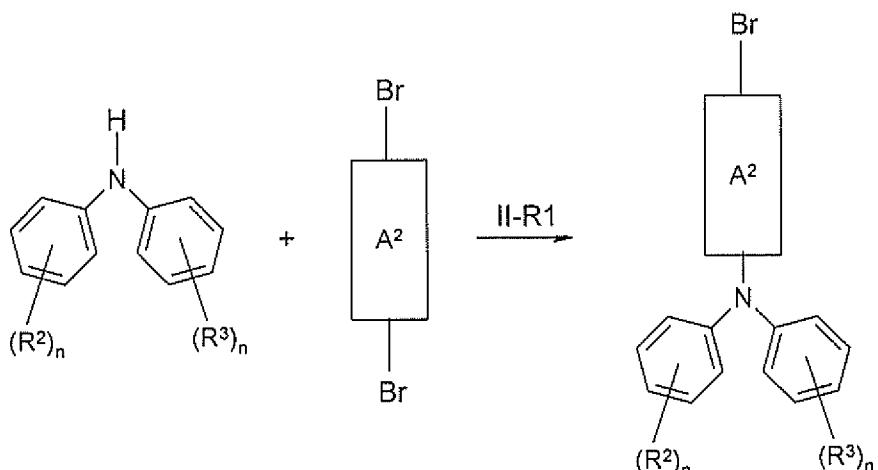
5 J. Grazulevicius; J. of Photochem. and Photobio., A: Chemistry 2004 162(2-3), 249-252.

The compounds of the formula I can be prepared via the sequence of synthesis steps shown above in synthesis route I. In steps (I-R1) to (I-R3), the reactants can be coupled, for example, by Ullmann reaction with copper as a catalyst or under palladium catalysis.

1.0

(b) *Synthesis route II:*

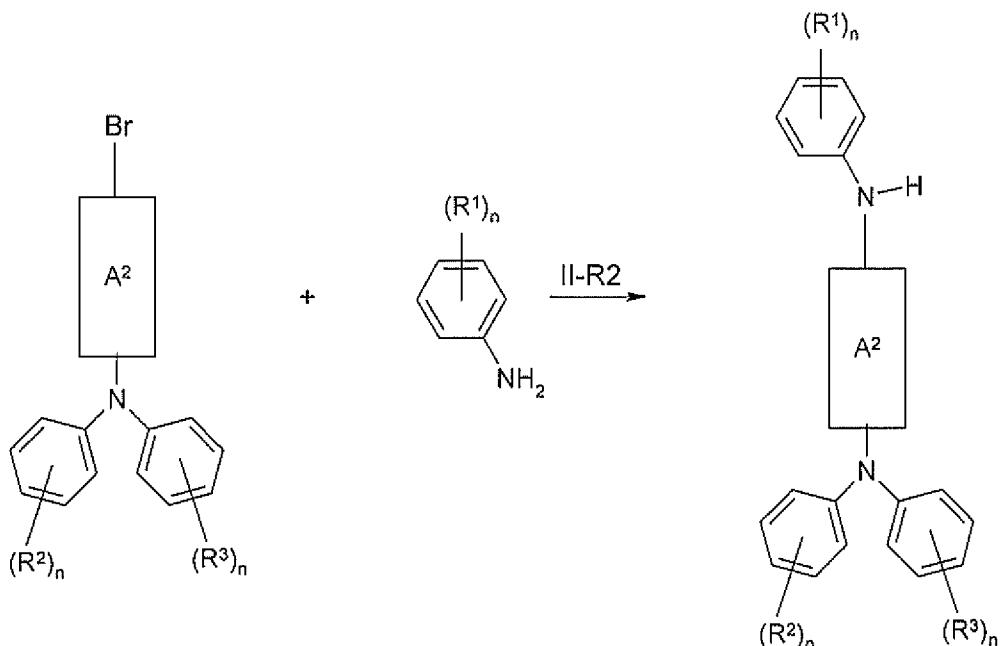
(b1) *Synthesis step II-R1:*



1.5

The synthesis in synthesis step II-R1 was based on the references cited under I-R2.

(b2) *Synthesis step II-R2:*



5

The synthesis in synthesis step II-R2 was based on the references cited below:

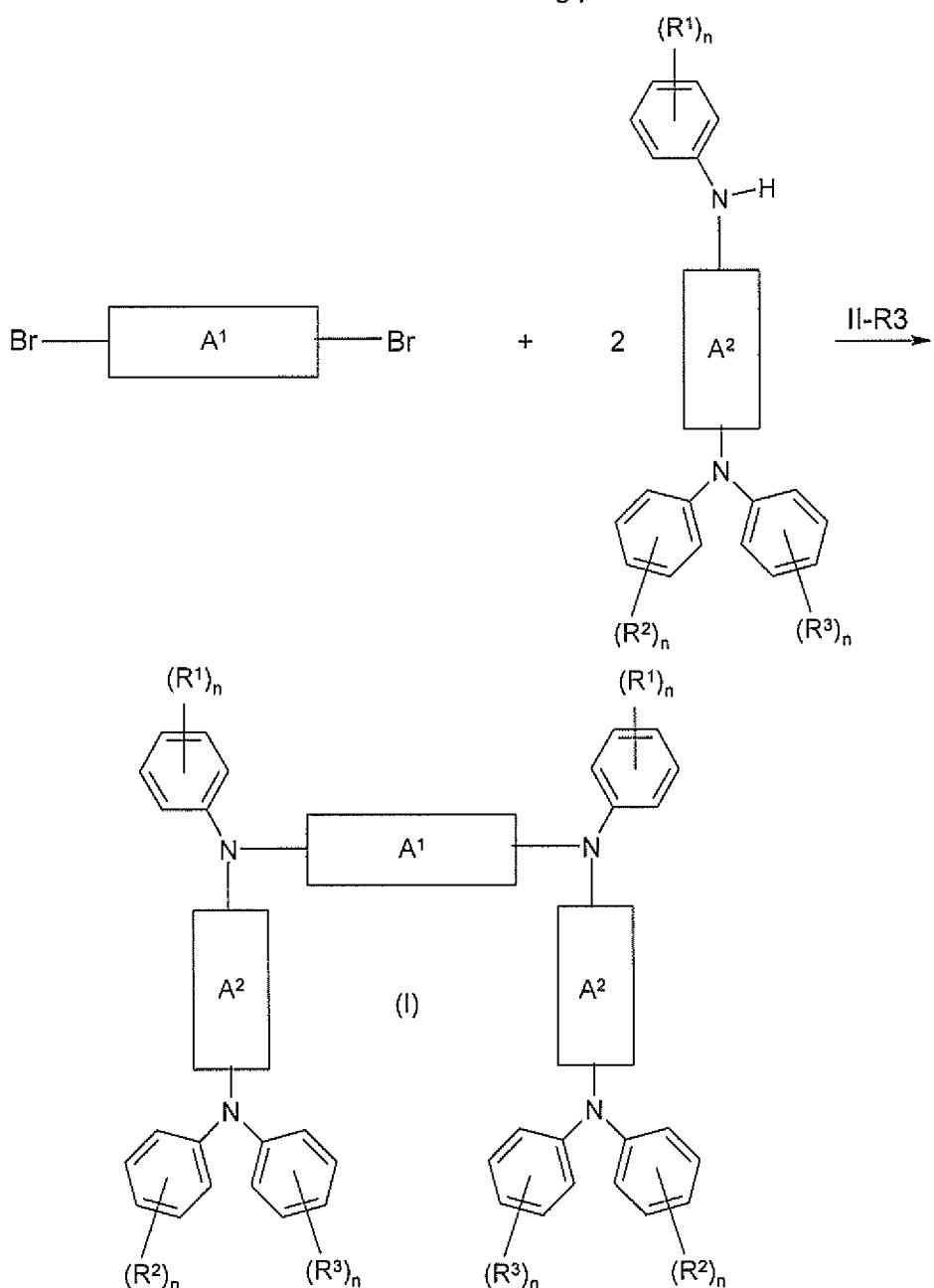
a) Bacher, Erwin; Bayerl, Michael; Rudati, Paula; Reckefuss, Nina; Müller, C. David; Meerholz, Klaus; Nuyken, Oskar; *Macromolecules*; 38; 5; 2005; 1640 – 1647,

10

b) Goodson, Felix E.; Hauck, Sheila; Hartwig, John F.; *J. Am. Chem. Soc.*; 121; 33; 1999; 7527 – 7539; Hauck, Sheila I.; Lakshmi, K. V.; Hartwig, John F.; *Org. Lett.*; 1; 13; 1999; 2057 – 2060.

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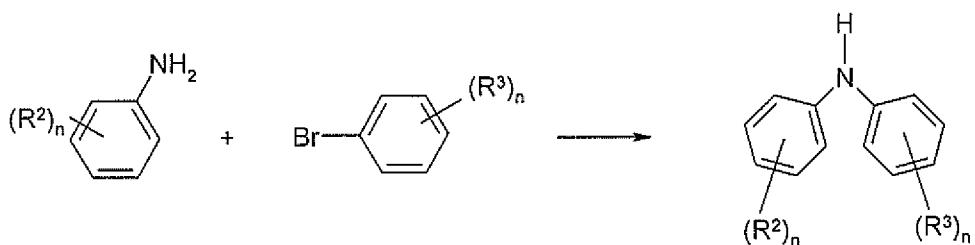
(b3) *Synthesis step II-R3:*



5 The compounds of the formula I can be prepared via the sequence of synthesis steps shown above in synthesis route II. In steps (II-R1) to (II-R3), the reactants can be coupled, as also in synthesis route I, for example, by Ullmann reaction with copper as a catalyst or under palladium catalysis.

(c) Preparation of the starting amines:

When the diarylamines in synthesis steps I-R2 and II-R1 of synthesis routes I and II are not commercially available, they can be prepared, for example, by Ullmann reaction with copper as a catalyst or under palladium catalysis, according to the following reaction:



5

The synthesis was based on the review articles listed below:

Palladium-catalyzed C-N coupling reactions:

10 a) Yang, Buchwald; J. Organomet. Chem. 1999, 576 (1-2), 125-146,

b) Wolfe, Marcoux, Buchwald; Acc. Chem. Res. 1998, 31, 805-818,

c) Hartwig; Angew. Chem. Int. Ed. Engl. 1998, 37, 2046-2067.

15

Copper-catalyzed C-N coupling reactions:

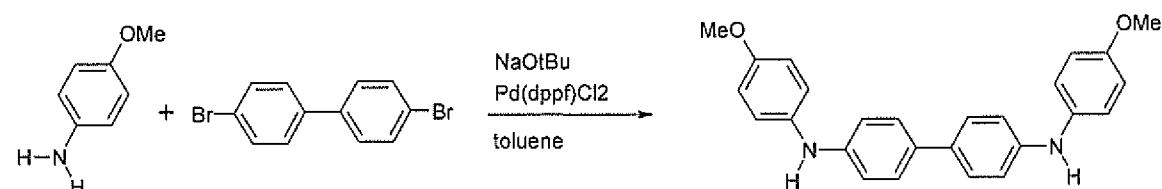
a) Goodbrand, Hu; Org. Chem. 1999, 64, 670-674,

b) Lindley; Tetrahedron 1984, 40, 1433-1456.

20

(B) Synthesis example 1: Synthesis of the compound ID367 (synthesis route I)

(B1): *Synthesis step according to general synthesis scheme I-R1:*

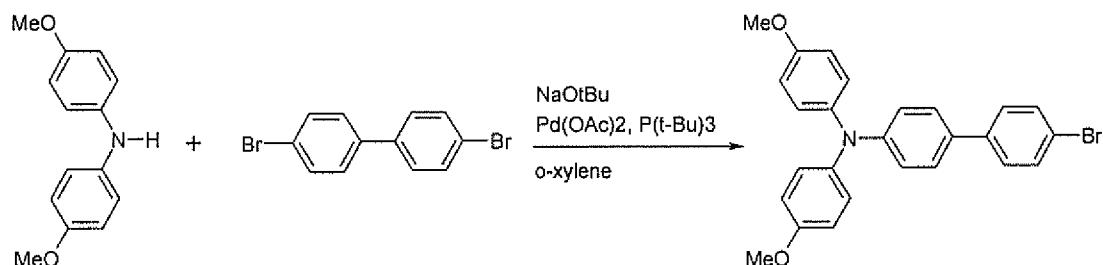


25 A mixture of 4,4'-dibromobiphenyl (93.6 g; 300 mmol), 4-methoxyaniline (133 g; 1.08 mol), Pd(dppf)Cl₂ (Pd(1,1'-bis(diphenylphosphino)ferrocene)Cl₂; 21.93 g; 30 mmol) and t-BuONa (sodium tert-butoxide; 109.06 g; 1.136 mol) in toluene (1500 ml) was stirred under a nitrogen atmosphere at 110°C for 24 hours. After cooling, the mixture was 30 diluted with diethyl ether and filtered through a Celite® pad (from Carl Roth). The filter

bed was washed with 1500 ml each of ethyl acetate, methanol and methylene chloride. The product was obtained as a light brown solid (36 g; yield: 30%).

10 ¹H NMR (400 MHz, DMSO): δ 7.81 (s, 2H), 7.34-7.32 (m, 4H), 6.99-6.97 (m, 4H), 6.90-6.88 (m, 4H), 6.81-6.79 (m, 4H), 3.64 (s, 6H).

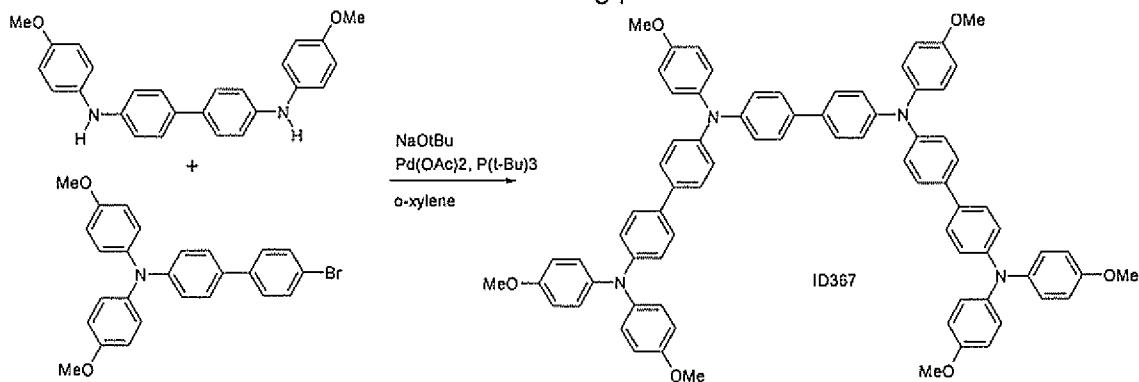
(B2): Synthesis step according to general synthesis scheme I-R2:



10 Nitrogen was passed for a period of 10 minutes through a solution of dppf (1,1'-bis(diphenyl-phosphino)ferrocene; 0.19 g; 0.34 mmol) and Pd₂(dba)₃ (tris(dibenzylideneacetone)-dipalladium(0); 0.15 g; 0.17 mmol) in toluene (220 ml). Subsequently, t-BuONa (2.8 g; 29 mmol) was added and the reaction mixture was stirred 15 for a further 15 minutes. 4,4'-Dibromobiphenyl (25 g; 80 mmol) and 4,4' - dimethoxydiphenylamine (5.52 g; 20 mmol) were then added successively. The reaction mixture was heated at a temperature of 100°C under a nitrogen atmosphere for 7 hours. After cooling to room temperature, the reaction mixture was quenched with ice-water, and the precipitated solid was filtered off and dissolved in ethyl acetate. The organic 20 layer was washed with water, dried over sodium sulfate and purified by column chromatography (eluent: 5% ethyl acetate/hexane). A pale yellow solid was obtained (7.58 g, yield: 82%).

25 ¹H NMR (300 MHz, DMSO-d₆): 7.60-7.49 (m, 6H), 7.07-7.04 (m, 4H), 6.94-6.91 (m, 4H), 6.83-6.80 (d, 2H), 3.75 (s, 6H).

(B3): Synthesis step according to general synthesis scheme I-R3:



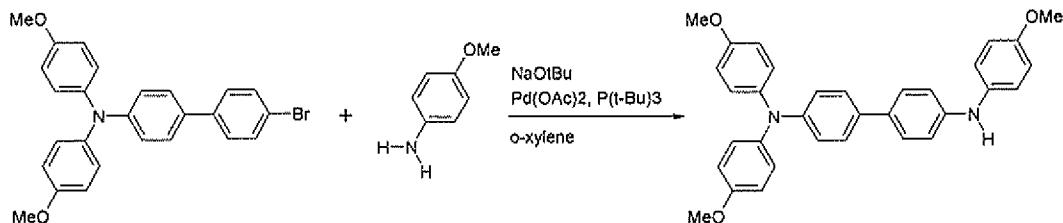
$N^4,N^{4\prime}$ -Bis(4-methoxyphenyl)biphenyl-4,4'-diamine (product from synthesis step I-R1; 0.4 g; 1.0 mmol) and product from synthesis step I-R2 (1.0 g; 2.2 mmol) were added under a nitrogen atmosphere to a solution of t-BuONa (0.32 g; 3.3 mmol) in o-xylene (25 ml).

5 Subsequently, palladium acetate (0.03 g; 0.14 mmol) and a solution of 10% by weight of P(t-Bu)₃ (tris-t-butylphosphine) in hexane (0.3 ml; 0.1 mmol) were added to the reaction mixture which was stirred at 125°C for 7 hours. Thereafter, the reaction mixture was 10 diluted with 150 ml of toluene and filtered through Celite®, and the organic layer was dried over Na₂SO₄. The solvent was removed and the crude product was reprecipitated three times from a mixture of tetrahydrofuran (THF)/methanol. The solid was purified by column chromatography (eluent: 20% ethyl acetate/hexane), followed by a precipitation with THF/methanol and an activated carbon purification. After removing the solvent, the product was obtained as a pale yellow solid (1.0 g, yield: 86%).

15 ¹H NMR (400 MHz, DMSO-d₆): 7.52-7.40 (m, 8H), 6.88-7.10 (m, 32H), 6.79-6.81 (d, 4H), 3.75 (s, 6H), 3.73 (s, 12H).

(C) Synthesis example 2: Synthesis of the compound ID447 (synthesis route II)

20 (C1) *Synthesis step according to general synthesis scheme II-R2:*

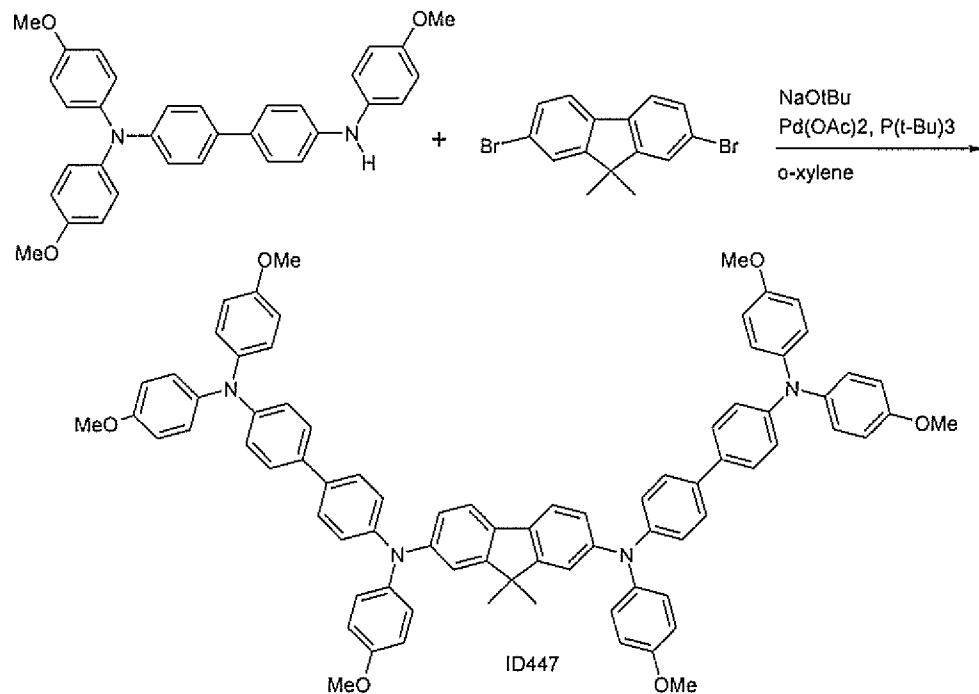


25 p-Anisidine (5.7 g, 46.1 mmol), t-BuONa (5.5 g, 57.7 mol) and P(t-Bu)₃ (0.62 ml, 0.31 mmol) were added to a solution of the product from synthesis step I-R2 (17.7 g, 38.4 mmol) in toluene (150 ml). After nitrogen had been passed through the reaction mixture for 20 minutes, Pd₂(dba)₃ (0.35 g, 0.38 mmol) was added. The resulting reaction mixture was left to stir under a nitrogen atmosphere at room temperature for 16 hours.

Subsequently, it was diluted with ethyl acetate and filtered through Celite®. The filtrate was washed twice with 150 ml each of water and saturated sodium chloride solution. After the organic phase had been dried over Na_2SO_4 and the solvent had been removed, a black solid was obtained. This solid was purified by column chromatography (eluent: 5 0– 25% ethyl acetate/hexane). This afforded an orange solid (14 g, yield: 75%).

^1H NMR (300 MHz, DMSO): 7.91 (s, 1H), 7.43-7.40 (d, 4H), 7.08-6.81 (m, 16H), 3.74 (s, 6H), 3.72 (s, 3H).

10 (C2) Synthesis step according to general synthesis scheme II-R3:



15 t-BuONa (686 mg; 7.14 mmol) was heated at 100°C under reduced pressure, then the reaction flask was purged with nitrogen and allowed to cool to room temperature. 2,7-Dibromo-9,9-dimethylfluorene (420 mg; 1.19 mmol), toluene (40 ml) and $\text{Pd}[\text{P}(\text{t-Bu})_3]_2$ (20 mg; 0.0714 mmol) were then added, and the reaction mixture was stirred at room temperature for 15 minutes. Subsequently, $\text{N,N,N',N'-p-trimethoxytriphenylbenzidine}$ (1.5 g; 1.27 mmol) was added to the reaction mixture which was stirred at 120°C for 5 hours. The mixture was filtered through a Celite®/ MgSO_4 mixture and washed with toluene. The crude product was purified twice by column chromatography (eluent: 30% ethyl acetate/hexane) and, after twice reprecipitating from THF/methanol, a pale yellow solid was obtained (200 mg, yield: 13%).

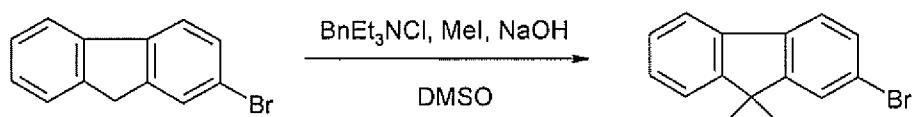
¹H NMR: (400 MHz, DMSO-d₆): 7.60-7.37 (m, 8H), 7.02-6.99 (m, 16H), 6.92-6.87 (m, 20H), 6.80-6.77 (d, 2H), 3.73 (s, 6H), 3.71 (s, 12H), 1.25 (s, 6H)

(D) Synthesis example 3: Synthesis of the compound ID453 (synthesis route I)

5

(D1) Preparation of the starting amine:

Step 1:



10

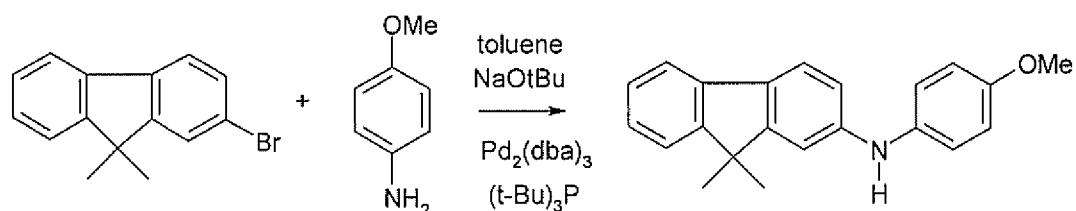
NaOH (78 g; 4 eq) was added to a mixture of 2-bromo-9H-fluorene (120 g; 1 eq) and BnEt₃NCl (benzyltriethylammonium chloride; 5.9 g; 0.06 eq) in 580 ml of DMSO (dimethyl sulfoxide). The mixture was cooled with ice-water, and methyl iodide (MeI) (160 g; 2.3 eq) was slowly added dropwise. The reaction mixture was left to stir overnight, then poured into water and subsequently extracted three times with ethyl acetate. The combined organic phases were washed with a saturated sodium chloride solution and dried over Na₂SO₄, and the solvent was removed. The crude product was purified by column chromatography using silica gel (eluent: petroleum ether). After washing with methanol, the product (2-bromo-9,9'-dimethyl-9H-fluorene) was obtained as a white solid (102 g).

15

20

¹H NMR (400 MHz, CDCl₃): δ 1.46 (s, 6 H), 7.32 (m, 2 H), 7.43 (m, 2 H), 7.55 (m, 2 H), 7.68 (m, 1 H)

25 Step 2:



p-Anisidine (1.23 g; 10.0 mmol) and 2-bromo-9,9'-dimethyl-9H-fluorene (3.0 g; 11.0 mmol) were added under a nitrogen atmosphere to a solution of t-BuONa (1.44 g; 15.0 mmol) in 15 ml of toluene (15 ml). Pd₂(dba)₃ (92 mg; 0.1 mmol) and a 10% by weight solution of P(t-Bu)₃ in hexane (0.24 ml; 0.08 mmol) were added, and the reaction mixture was stirred at room temperature for 5 hours. Subsequently, the mixture was quenched with ice-water, and the precipitated solid was filtered off and dissolved in ethyl

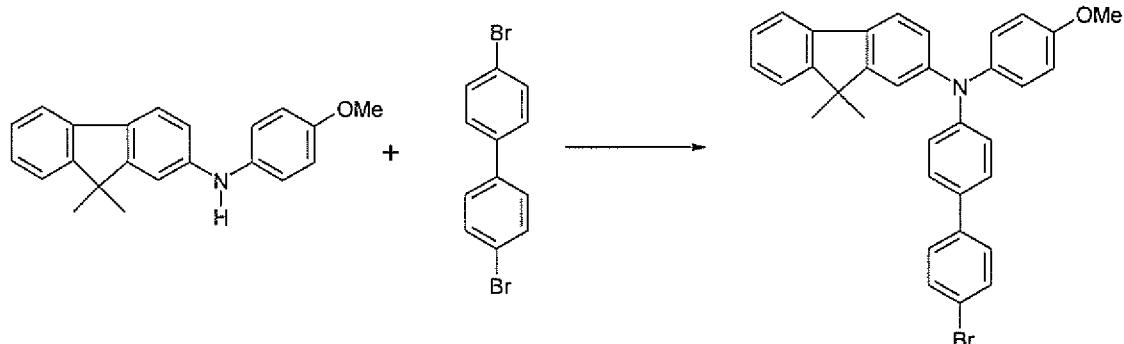
acetate. The organic phase was washed with water and dried over Na_2SO_4 . After purifying the crude product by column chromatography (eluent: 10% ethyl acetate/hexane), a pale yellow solid was obtained (1.5 g, yield: 48%).

5 ^1H NMR (300 MHz, C_6D_6): 7.59-7.55 (d, 1H), 7.53-7.50 (d, 1H), 7.27-7.22 (t, 2H), 7.19 (s, 1H), 6.99-6.95 (d, 2H), 6.84-6.77 (m, 4H), 4.99 (s, 1H), 3.35 (s, 3H), 1.37 (s, 6H).

(D2) Preparation of the compound ID453 for use in accordance with the invention

(D2.1): Synthesis step according to general synthesis scheme I-R2:

10



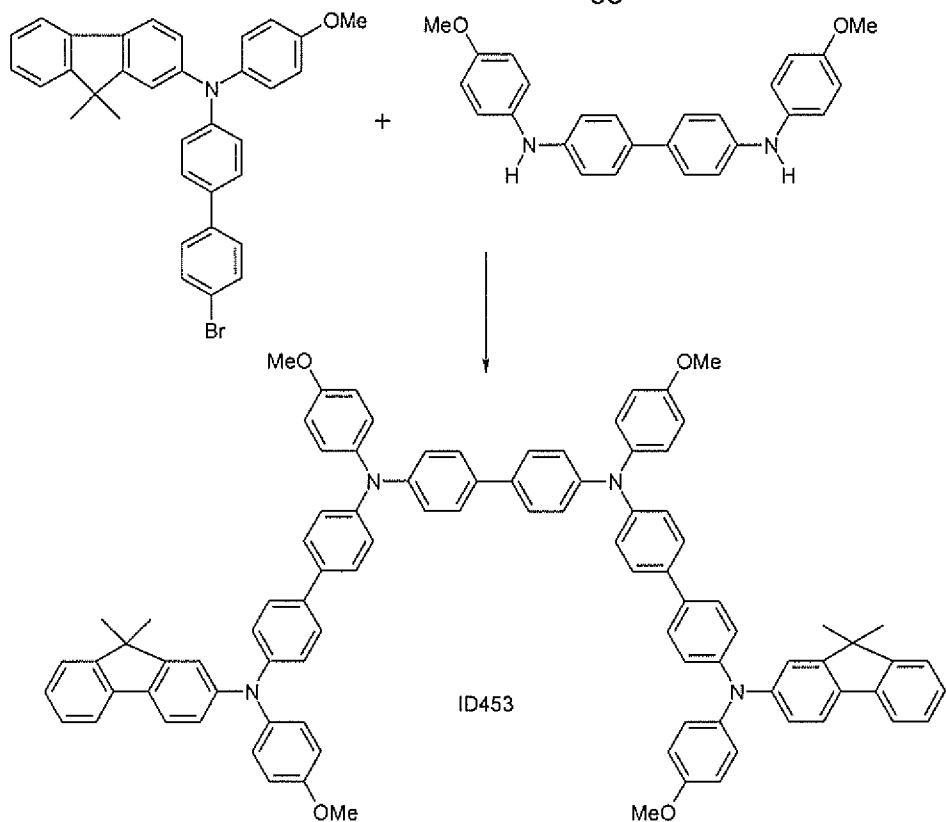
Product from a) (4.70 g; 10.0 mmol) and 4,4' -dibromobiphenyl (7.8 g; 25 mmol) were added to a solution of t-BuONa (1.15 g; 12 mmol) in 50 ml of toluene under nitrogen. $\text{Pd}_2(\text{dba})_3$ (0.64 g; 0.7 mmol) and DPPF (0.78 g; 1.4 mmol) were added, and the reaction mixture was left to stir at 100°C for 7 hours. After the reaction mixture had been quenched with ice-water, the precipitated solid was filtered off and it was dissolved in ethyl acetate. The organic phase was washed with water and dried over Na_2SO_4 . After purifying the crude product by column chromatography (eluent: 1% ethyl acetate/hexane), a pale yellow solid was obtained (4.5 g, yield: 82%).

15

20 ^1H NMR (400 MHz, DMSO-d6): 7.70-7.72 (d, 2H), 7.54-7.58 (m, 6H), 7.47-7.48 (d, 1H), 7.21-7.32 (m, 3H), 7.09-7.12 (m, 2H), 6.94-6.99 (m, 4H), 3.76 (s, 3H), 1.36 (s, 6H).

(D2.2) Synthesis step according to general synthesis scheme I-R3:

25



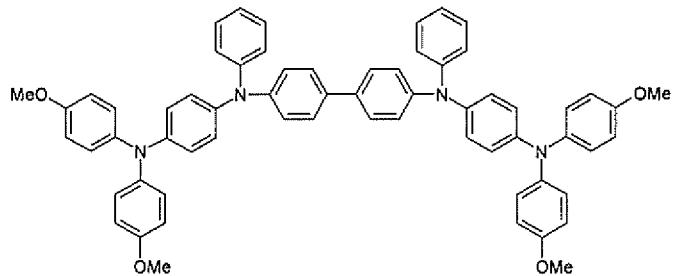
N⁴,N^{4'}-Bis(4-methoxyphenyl)biphenyl-4,4'-diamine (0.60 g; 1.5 mmol) and product from the preceding synthesis step I-R2 (1.89 g; 3.5 mmol) were added under nitrogen to a 5 solution of t-BuONa (0.48 g; 5.0 mmol) in 30 ml of o-xylene. Palladium acetate (0.04 g; 0.18 mmol) and P(t-Bu)₃ in a 10% by weight solution in hexane (0.62 ml; 0.21 mmol) were added, and the reaction mixture was stirred at 125°C for 6 hours. Subsequently, the mixture was diluted with 100 ml of toluene and filtered through Celite®. The organic 10 phase was dried over Na₂SO₄ and the resulting solid was purified by column chromatography (eluent: 10% ethyl acetate/hexane). This was followed by reprecipitation from THF/methanol to obtain a pale yellow solid (1.6 g, yield: 80%).

15 ¹H NMR (400 MHz, DMSO-d₆): 7.67-7.70 (d, 4H), 7.46-7.53 (m, 14H), 7.21-7.31 (m, 4H), 7.17-7.18 (d, 2H), 7.06-7.11 (m, 8H), 6.91-7.01 (m, 22H), 3.75 (s, 12H), 1.35 (s, 12H).

(E) Further compounds of the formula I for use in accordance with the invention:

20 The compounds listed below were obtained analogously to the syntheses described above:

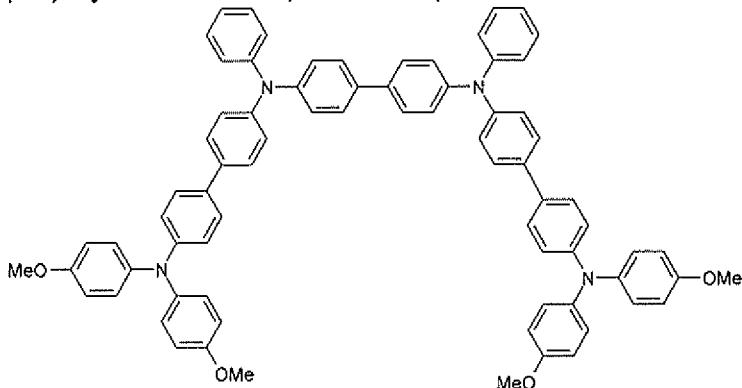
(E1) Synthesis example 4: Compound ID320



¹H NMR (300 MHz, THF-d₈): δ 7.43-7.46 (d, 4H), 7.18-7.23 (t, 4H), 7.00-7.08 (m, 16H), 6.81-6.96 (m, 18H), 3.74 (s, 12H)

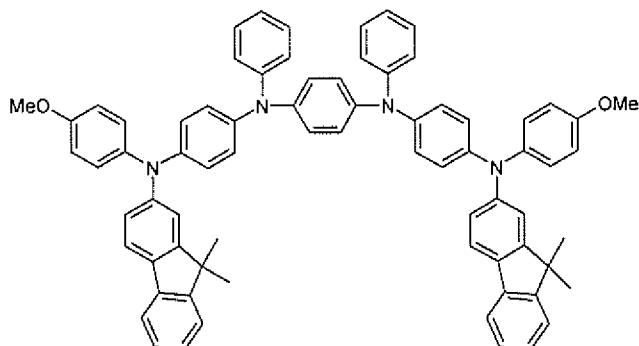
5

(E2) Synthesis example 5: Compound ID321



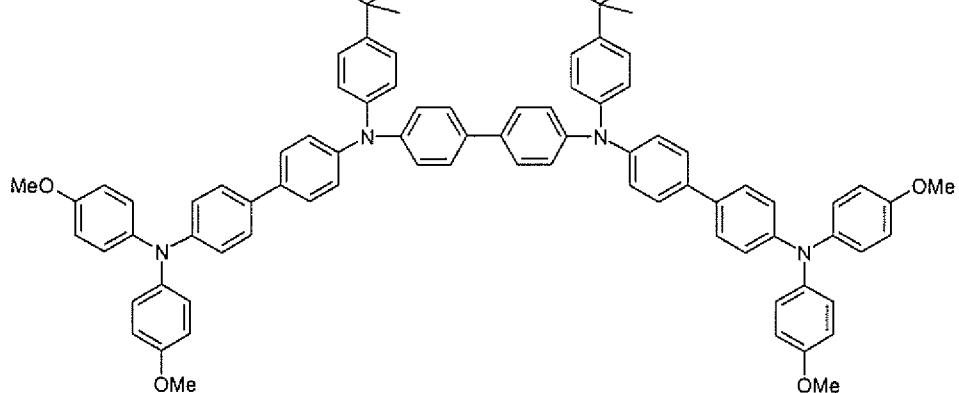
¹H NMR (300 MHz, THF-d₈): δ 7.37-7.50 (t, 8H), 7.37-7.40 (d, 4H), 7.21-7.26 (d, 4H), 6.96-7.12 (m, 22H), 6.90-6.93 (d, 4H), 6.81-6.84 (d, 8H), 3.74 (s, 12H)

(E3) Synthesis example 6: Compound ID366



¹H NMR (400 MHz, DMSO-d6): δ 7.60-7.70 (t, 4H), 7.40-7.55 (d, 2H), 7.17-7.29 (m, 8H), 7.07-7.09 (t, 4H), 7.06 (s, 2H), 6.86-7.00 (m, 24H), 3.73 (s, 6H), 1.31 (s, 12H)

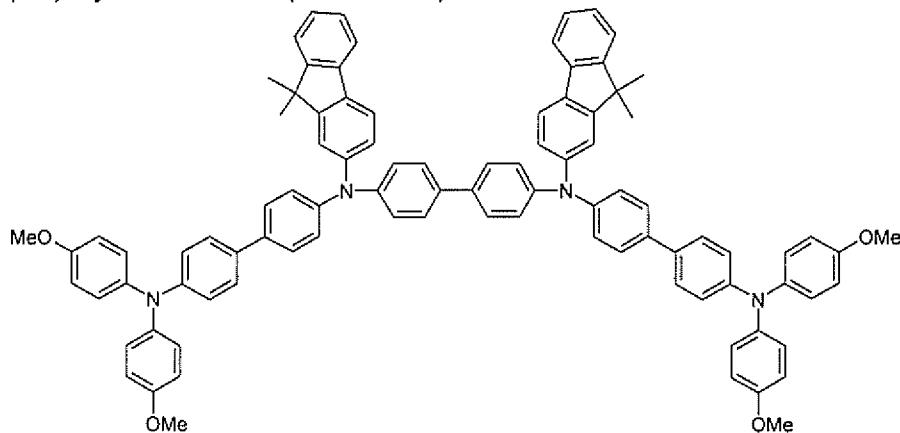
(E4) Synthesis example 7: Compound ID368



¹H NMR (400 MHz, DMSO-d6): δ 7.48-7.55 (m, 8H), 7.42-7.46 (d, 4H), 7.33-7.28 (d, 4H), 6.98-7.06 (m, 20H), 6.88-6.94 (m, 8H), 6.78-6.84 (d, 4H), 3.73 (s, 12H), 1.27 (s, 18H)

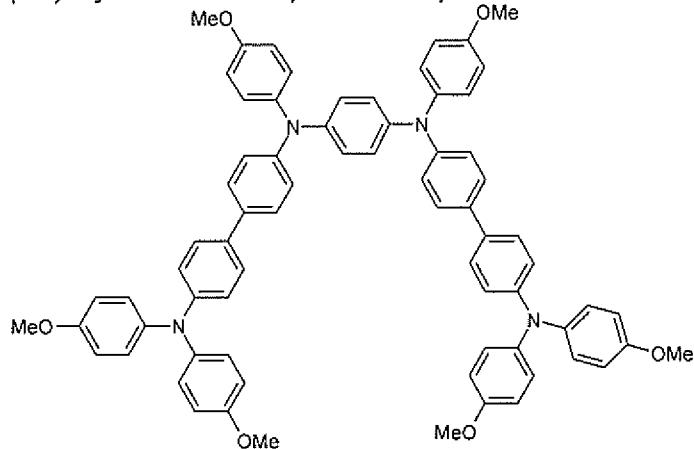
5

(E5) Synthesis example 8: Compound ID369



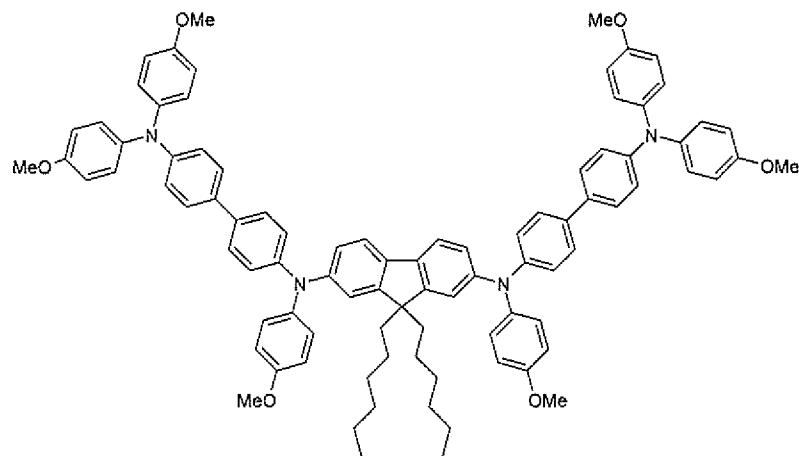
¹H NMR (400 MHz, THF-d8): δ 7.60-7.70 (t, 4H), 7.57-7.54 (d, 4H), 7.48-7.51 (d, 4H),
10 7.39-7.44 (t, 6H), 7.32-7.33 (d, 2H), 7.14-7.27 (m, 12H), 7.00-7.10 (m, 10H), 6.90-6.96 (m, 4H), 6.80-6.87 (m, 8H), 3.75 (s, 12H), 1.42 (s, 12H)

(E6) Synthesis example 9: Compound ID446



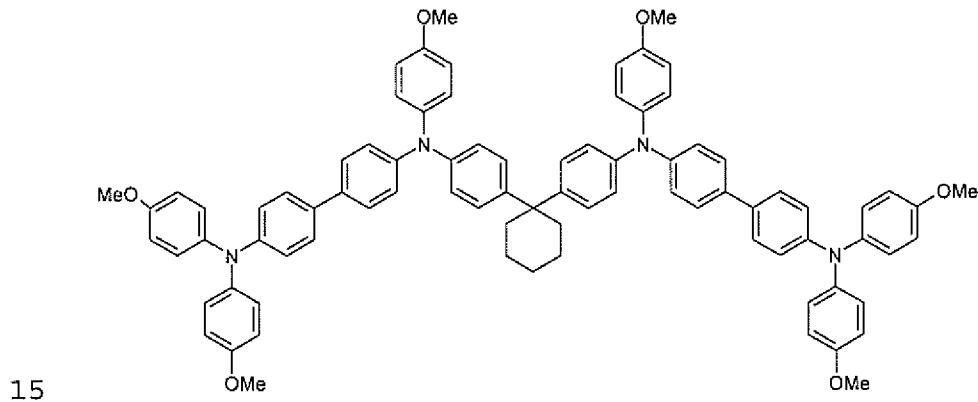
¹H NMR (400 MHz, dmso-d₆): δ 7.39-7.44 (m, 8H), 7.00-7.07 (m, 13H), 6.89-6.94 (m, 19H), 6.79-6.81 (d, 4H), 3.73 (s, 18H)

5 (E7) *Synthesis example 10: Compound ID450*



¹H NMR (400 MHz, dmso-d₆): δ 7.55-7.57 (d, 2H), 7.39-7.45 (m, 8H), 6.99-7.04 (m, 15H),
10 6.85-6.93 (m, 19H), 6.78-6.80 (d, 4H), 3.72 (s, 18H), 1.68-1.71 (m, 6H), 1.07 (m, 6H),
0.98-0.99 (m, 8H), 0.58 (m, 6H)

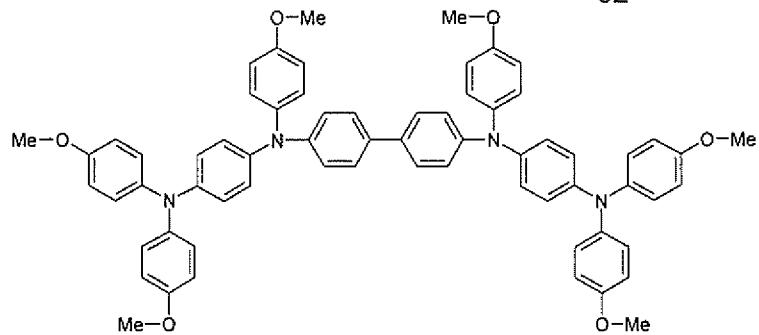
(E8) *Synthesis example 11: Compound ID452*



¹H NMR (400 MHz, DMSO-d₆): δ 7.38-7.44 (m, 8H), 7.16-7.19 (d, 4H), 6.99-7.03 (m, 12H), 6.85-6.92 (m, 20H), 6.77-6.79 (d, 4H), 3.74 (s, 18H), 2.00-2.25 (m, 4H), 1.25-1.50 (m, 6H)

20

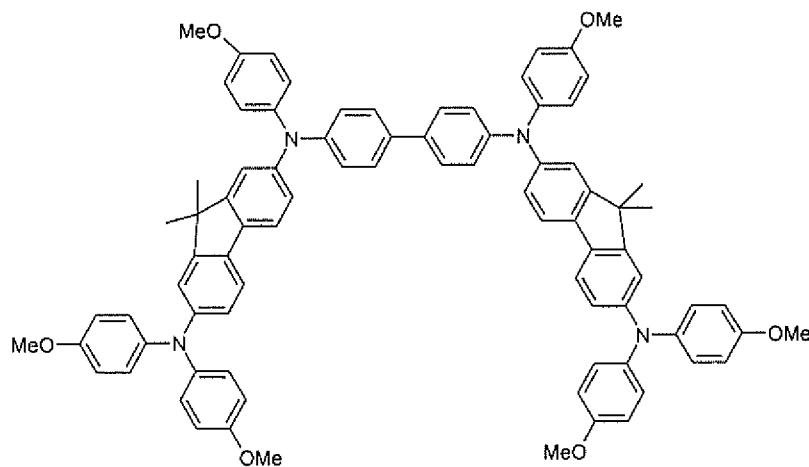
(E9) *Synthesis example 12: Compound ID480*



10 ^1H NMR (400 MHz, DMSO-d6): δ 7.40-7.42 (d, 4H), 7.02-7.05 (d, 4H), 6.96-6.99 (m, 28H), 6.74-6.77 (d, 4H), 3.73 (s, 6H), 3.71 (s, 12H)

5

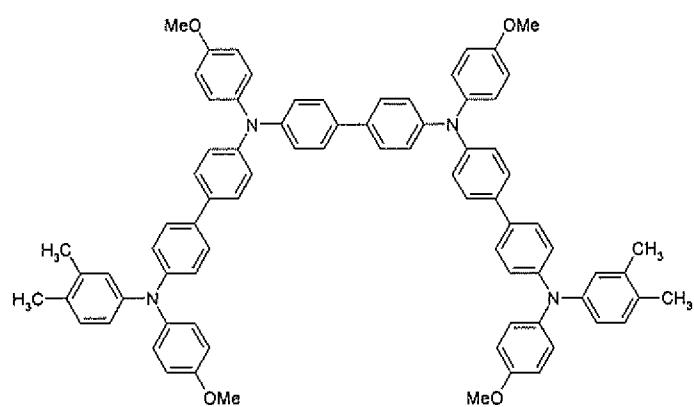
(E10) *Synthesis example 13: Compound ID518*



10 ^1H NMR (400 MHz, DMSO-d6): 7.46-7.51 (m, 8H), 7.10-7.12 (d, 2H), 7.05-7.08 (d, 4H), 6.97-7.00 (d, 8H), 6.86-6.95 (m, 20H), 6.69-6.72 (m, 2H), 3.74 (s, 6H), 3.72 (s, 12H), 1.24 (t, 12H)

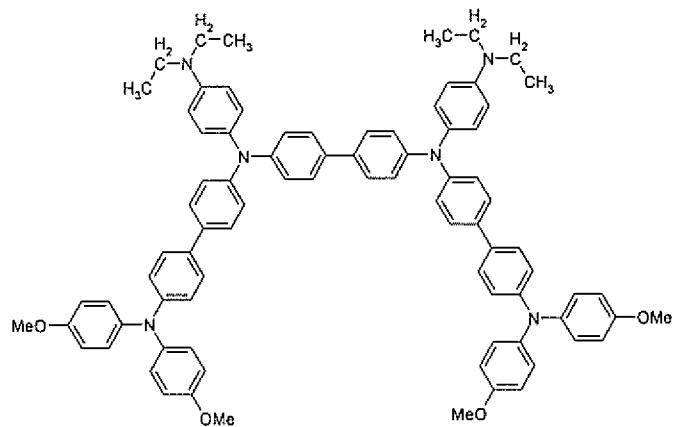
(E11) *Synthesis example 14: Compound ID519*

15



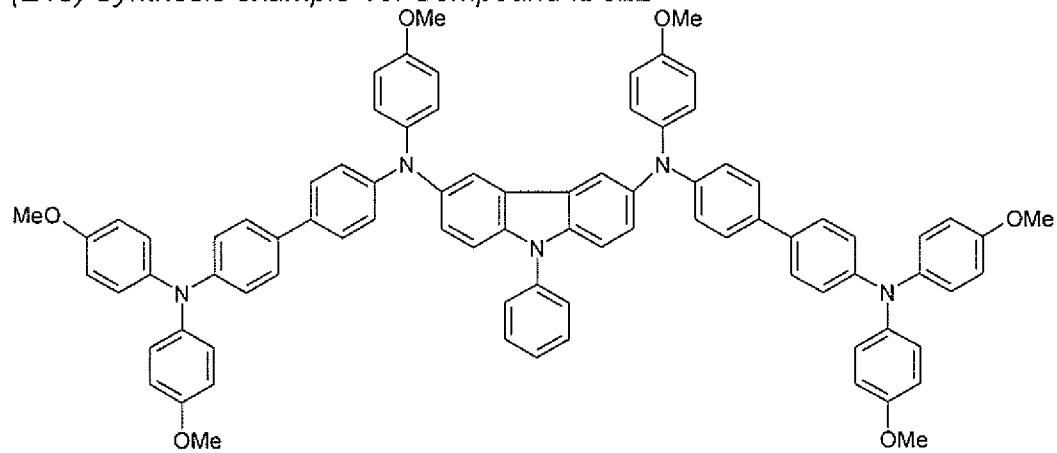
¹H NMR (400 MHz, DMSO-d6): 7.44-7.53 (m, 12H), 6.84-7.11 (m, 32H), 6.74-6.77 (d, 2H), 3.76 (s, 6H), 3.74 (s, 6H), 2.17 (s, 6H), 2.13 (s, 6H)

5 (E12) Synthesis example 15: Compound ID521



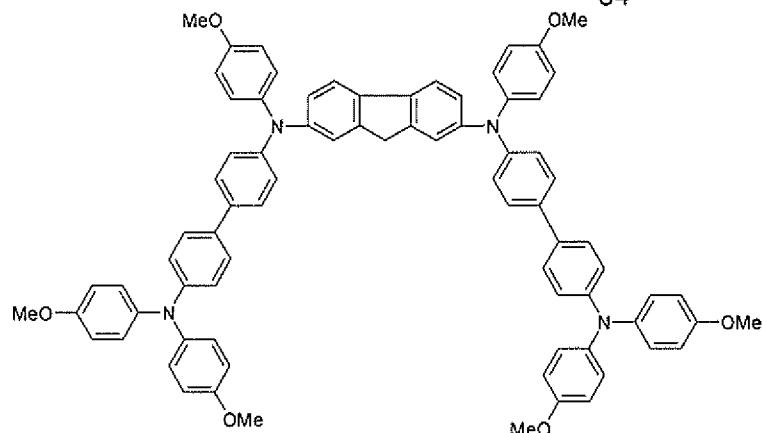
10 ^1H NMR (400 MHz, THF- d_6): 7.36-7.42 (m, 12H), 6.99-7.07 (m, 20H), 6.90-6.92 (d, 4H),
6.81-6.84 (m, 8H), 6.66-6.69 (d, 4H), 3.74 (s, 12H), 3.36-3.38 (q, 8H), 1.41-1.17 (t, 12H)

(E13) Synthesis example 16: Compound ID522



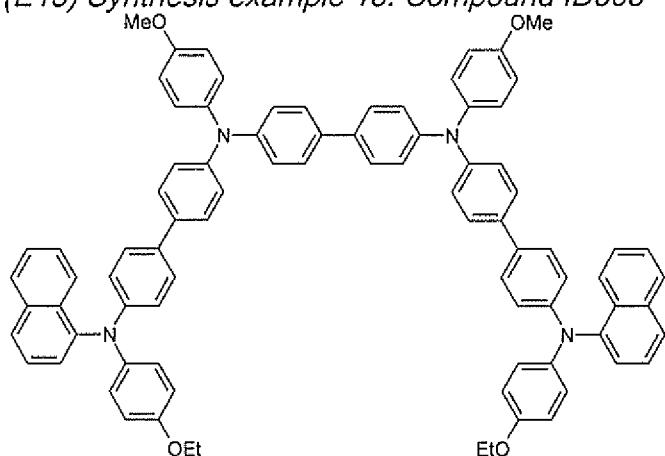
15 ^1H NMR (400 MHz, DMSO- d_6): 7.65 (s, 2H), 7.52-7.56 (t, 2H), 7.44-7.47 (t, 1H), 7.37-7.39 (d, 2H), 7.20-7.22 (m, 10H), 7.05-7.08 (dd, 2H), 6.86-6.94 (m, 8H), 6.79-6.80-6.86 (m, 12H), 6.68-6.73, (dd, 8H), 6.60-6.62 (d, 4H), 3.68 (s, 12H), 3.62 (s, 6H)

(E14) Synthesis example 17: Compound ID523



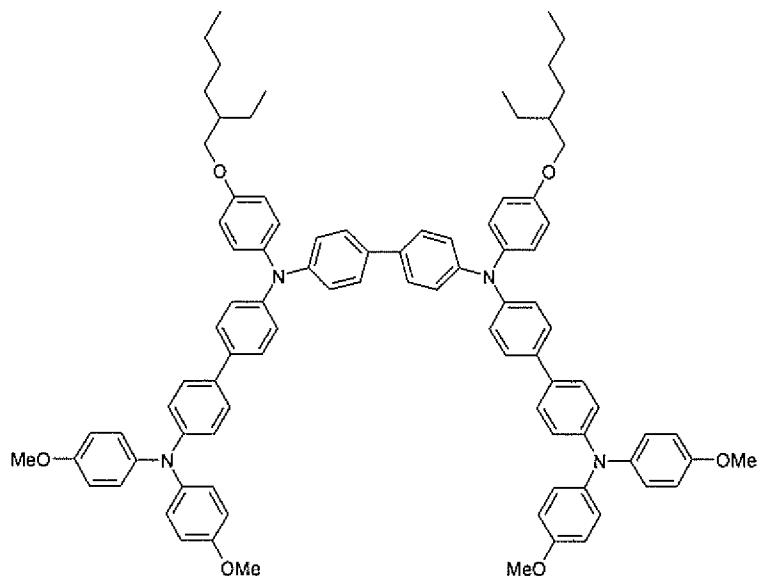
¹H NMR (400 MHz, THF-d₈): 7.54-7.56 (d, 2H), 7.35-7.40 (dd, 8H), 7.18 (s, 2H), 7.00-7.08 (m, 18H), 6.90-6.92 (d, 4H), 6.81-6.86 (m, 12H), 3.75 (s, 6H), 3.74 (s, 12H), 3.69 (s, 2H))

(E15) Synthesis example 18: Compound ID565



10 ¹H NMR (400 MHz, THF-d8): 7.97-8.00 (d, 2H), 7.86-7.89 (d, 2H), 7.73-7.76 (d, 2H), 7.28-7.47 (m, 20H), 7.03-7.08 (m, 16H), 6.78-6.90 (m, 12H), 3.93-3.99 (q, 4H), 3.77 (s, 6H), 1.32-1.36 (s, 6H)

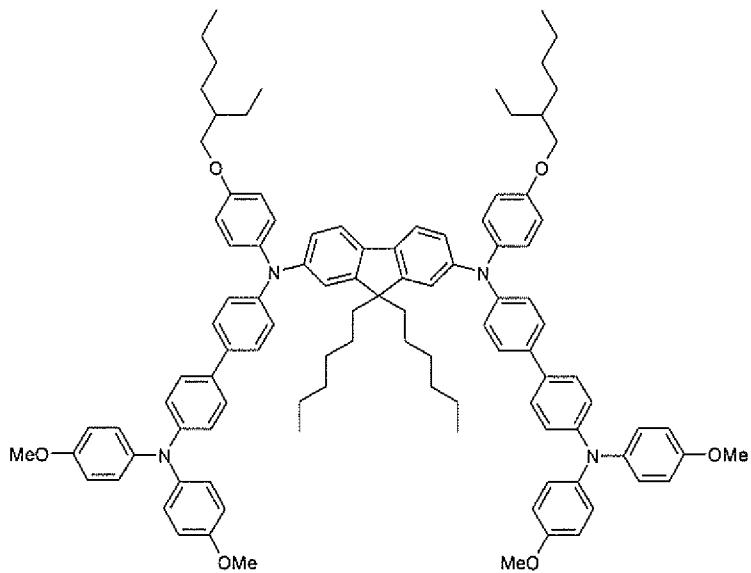
(E16) Synthesis example 19: Compound ID568



¹H NMR (400 MHz, DMSO-d6): 7.41-7.51 (m, 12H), 6.78-7.06 (m, 36H), 3.82-3.84 (d, 4H), 3.79 (s, 12H), 1.60-1.80 (m, 2H), 0.60-1.60 (m, 28H)

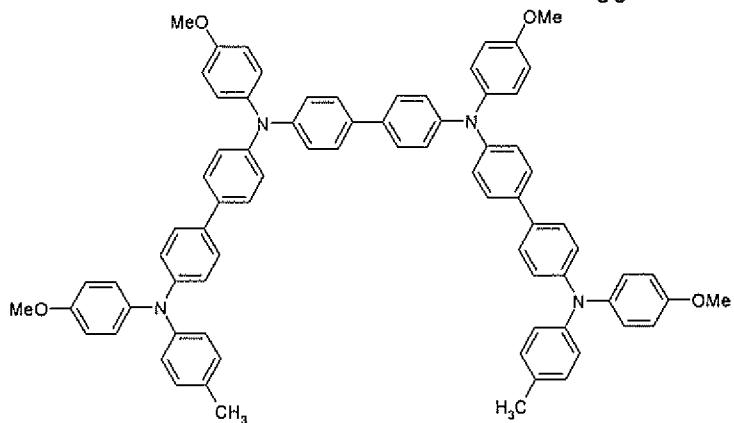
5

(E17) Synthesis example 20: Compound ID569



10 ¹H NMR (400 MHz, DMSO-d6): 7.40-7.70 (m, 10H), 6.80-7.20 (m, 36H), 3.92-3.93 (d, 4H), 2.81 (s, 12H), 0.60-1.90 (m, 56H)

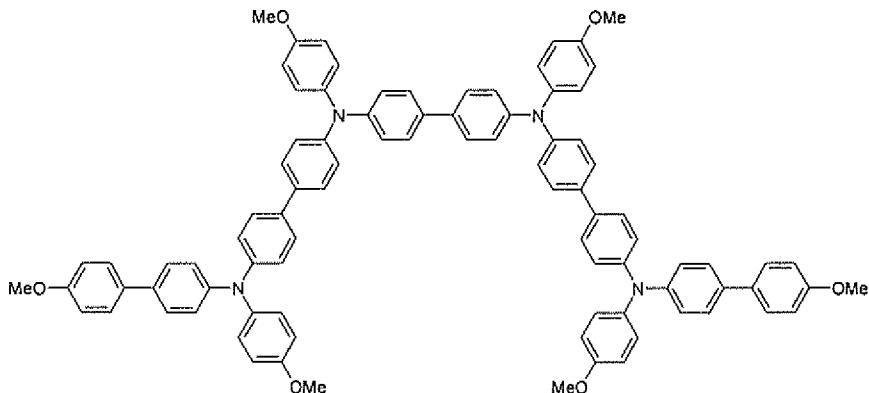
(E18) Synthesis example 21: Compound ID572



¹H NMR (400 MHz, THF-d8): 7.39-7.47 (m, 12H), 7.03-7.11 (m, 20H), 6.39-6.99 (m, 8H), 6.83-6.90 (m, 8H), 3.78 (s, 6H), 3.76 (s, 6H), 2.27 (s, 6H)

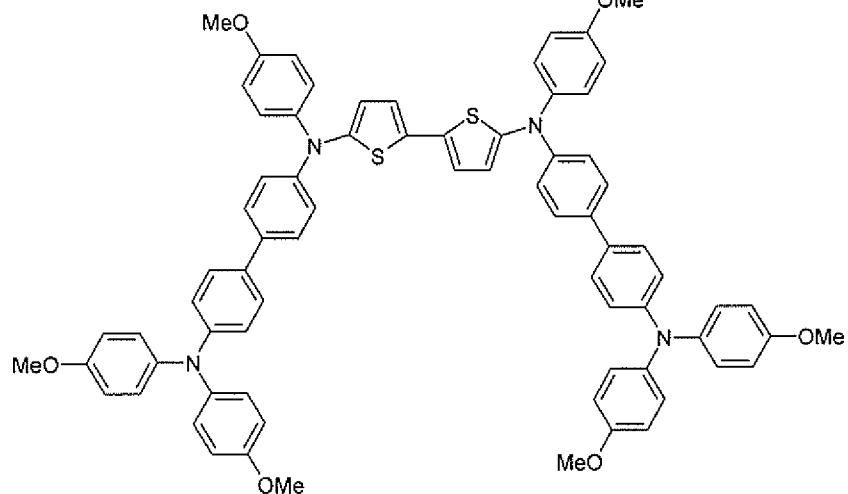
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(E19) *Synthesis example 22: Compound ID573*



10 ¹H NMR (400 MHz, THF-d8): 7.43-7.51 (m, 20H), 7.05-7.12 (m, 24H), 6.87-6.95 (m, 12H), 3.79 (s, 6H), 3.78 (s, 12H)

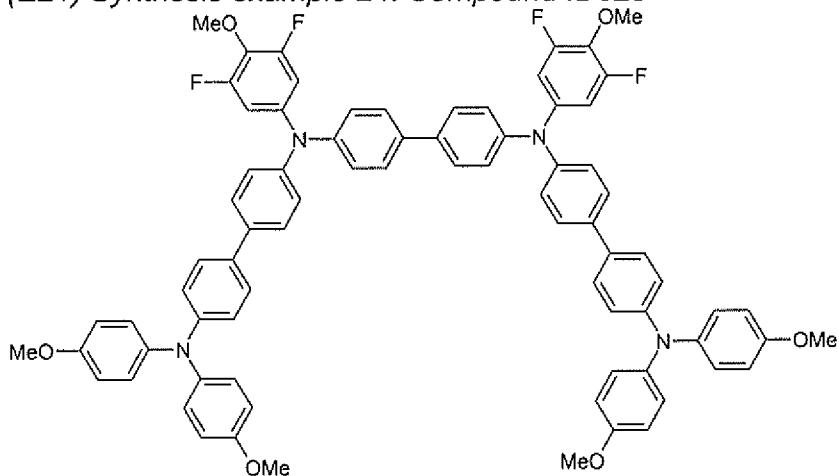
(E20) *Synthesis example 23: Compound ID575*



¹H NMR (400 MHz, DMSO-d₆): 7.35-7.55 (m, 8H), 7.15-7.45 (m, 4H), 6.85-7.10 (m, 26H), 6.75-6.85 (d, 4H), 6.50-6.60 (d, 2H), 3.76 (s, 6H), 3.74 (s, 12H)

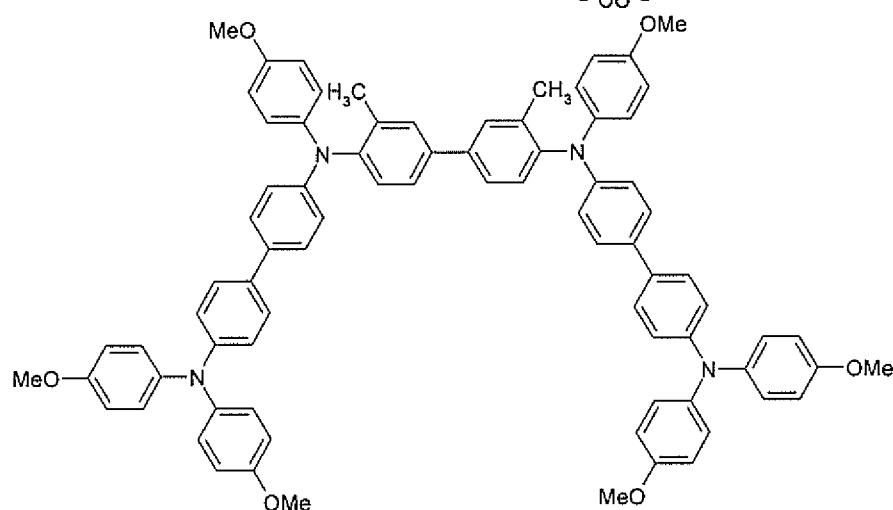
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(E21) Synthesis example 24: Compound ID629



¹H NMR (400 MHz, THF-d₈): 7.50-7.56 (dd, 8H), 7.38-7.41 (dd, 4H), 7.12-7.16 (d, 8H),
1.0 7.02-7.04 (dd, 8H), 6.91-6.93 (d, 4H), 6.82-6.84 (dd, 8H), 6.65-6.68 (d, 4H) 3.87 (s, 6H),
3.74 (s, 12H)

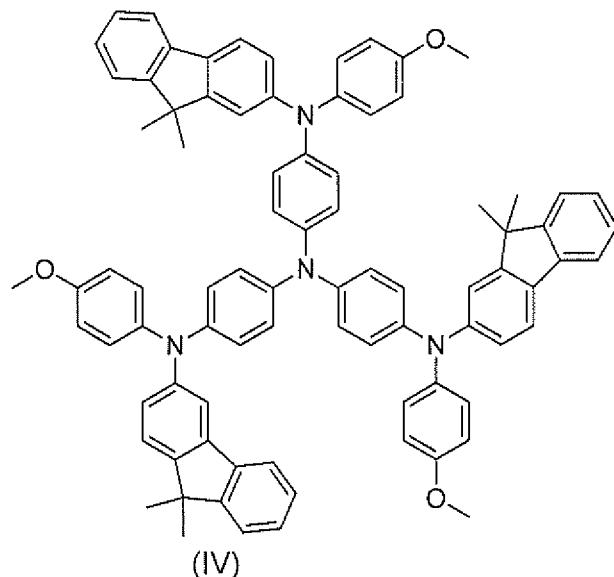
(E22) Synthesis example 25: Compound ID631



¹H NMR (400 MHz, THF-d₆): 7.52 (d, 2H), 7.43-7.47 (dd, 2H), 7.34-7.38 (m, 8H), 7.12-7.14 (d, 2H), 6.99-7.03 (m, 12H), 6.81-6.92 (m, 20H), 3.74 (s, 18H), 2.10 (s, 6H)

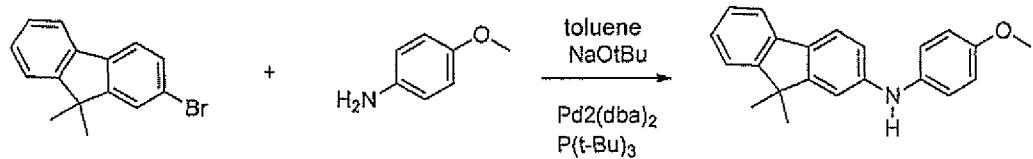
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(F) Synthesis of compounds of the formula IV:



10

(a) Coupling of p-anisidine and 2-bromo-9,9-dimethyl-9H-fluorene



15

To 0.24 ml (0.08 mmol) of $P(t\text{-}Bu)_3$ ($d = 0.68 \text{ g/ml}$) and 0.1 g of $Pd_2(dbu)_2$ [=tris(dibenzylideneacetone)dipalladium(0)] (0.1 mmol) were added 10 ml to 15 ml of toluene (anhydrous, 99.8%), and the mixture was stirred at room temperature for 10 min. 1.44 g (15 mmol) of sodium tert-butoxide (97.0%) were added and the mixture was 5 stirred at room temperature for a further 15 min. Subsequently, 2.73 g (11 mmol) of 2-bromo-9,9-dimethyl-9H-fluorene were added and the reaction mixture was stirred for a further 15 min. Finally, 1.23 g (10 mmol) of p-anisidine were added and the mixture was stirred at 90°C for 4 h.

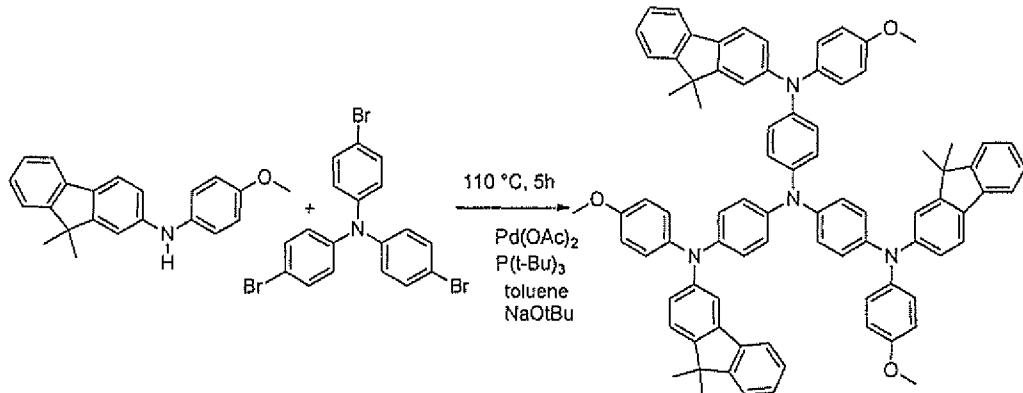
10 The reaction mixture was admixed with water and the product was precipitated from hexane. The aqueous phase was additionally extracted with ethyl acetate. The organic phase and the precipitated solid which had been filtered off were combined and purified by column chromatography on an SiO_2 phase (10:1 hexane:ethyl acetate).

15 1.5 g (yield: 47.6%) of a yellow solid were obtained.

^1H NMR (300 MHz, C_6D_6): 6.7-7.6 (m, 11H), 5.00 (s, 1H,), 3.35 (s, 3H), 1.37 (s, 6H)

(b) Coupling of the product from (a) with tris(4-bromophenyl)amine

20



To 0.2 ml (0.07 mmol) of $P(t\text{-}Bu)_3$ ($D = 0.68 \text{ g/ml}$) and 0.02 g (0.1 mmol) of palladium acetate were added 25 ml of toluene (anhydrous), and the mixture was stirred at room 25 temperature for 10 min. 0.4 g (1.2 mmol) of sodium tert-butoxide (97.0%) was added and the mixture was stirred at room temperature for a further 15 min. Subsequently, 0.63 g (1.3 mmol) of tris(4-bromophenyl)amine was added and the reaction mixture was stirred for a further 15 min. Finally, 1.3 g (1.4 mmol) of the product from step (a) were added and the mixture was stirred at 90°C for 5 h.

30

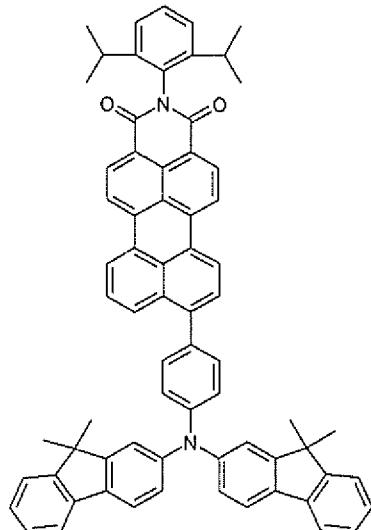
The reaction mixture was admixed with ice-cold water and extracted with ethyl acetate. The product was precipitated from a mixture of hexane/ethyl acetate and purified by column chromatography on SiO₂ phase (9:1 → 5:1 hexane:ethyl acetate gradient).

5 0.7 g (yield: 45%) of a yellow product was obtained.

¹HNMR (300 MHz, C₆D₆): 6.6-7.6 (m, 45H), 3.28 (s, 9H), 1.26 (s, 18H)

(G) Synthesis of compounds ID504:

10



15 The preparation proceeded from (4-bromophenyl)bis(9,9-dimethyl-9H-fluoren-2-yl) (see Chemical Communications, 2004, 68-69), which was first reacted with 4,4,5,5,4',4',5',5'-octamethyl-[2,2']bi[[1,3,2]dioxaborolanyl] (step a). This was followed by coupling with 9Br-DIPP-PDCI (step b). This was followed by hydrolysis to give the anhydride (step c) and subsequent reaction with glycine to give the final compound (step d).

Step a:

20

A mixture of 30 g (54 mmol) of (4-bromophenyl)bis(9,9-dimethyl-9H-fluoren-2-yl), 41 g (162 mmol) of 4,4,5,5,4',4',5',5'-octamethyl-[2,2']bi[[1,3,2]dioxaborolanyl], 1 g (1.4 mmol) of Pd(dpdpf)₂Cl₂, 15.9 g (162 mmol) of potassium acetate and 300 ml of dioxane was heated to 80°C and stirred for 36 h.

25

After cooling, the solvent was removed and the residue was dried at 50°C in a vacuum drying cabinet.

Purification was effected by filtration through silica gel with the eluent 1:1 n-hexane:dichloromethane. After the removal of the reactant, the eluent was switched to dichloromethane. The product was isolated as a reddish and tacky residue. This was extracted by stirring with methanol at RT for 0.5 h. The light-colored precipitate was 5 filtered off. After drying at 45°C in a vacuum drying cabinet, 24 g of a light-colored solid were obtained, which corresponds to a yield of 74%.

Analytic data

10 ^1H NMR (500MHz, CD_2Cl_2 , 25°C): δ = 7.66-7.61 (m, 6H); 7.41-7.4 (m, 2H); 7.33-7.25 (m, 6H); 7.13-7.12 (m, 2H); 7.09-7.07 (m, 2H); 1.40 (s, 12H); 1.32 (s, 12H)

Step b:

15 17.8 g (32 mmol) of 9Br-DIPP-PDCI and 19 ml (95 mmol) of 5 molar NaOH were introduced into 500 ml of dioxane. This mixture was degassed with argon for 30 min. Then 570 mg (1.1 mmol) of $\text{Pd}[\text{P}(\text{tBu})_3]_2$ and 23 g (38 mmol) of stage a were added and the mixture was stirred at 85°C under argon for 17 h.

20 Purification was effected by column chromatography with the eluent 4:1 dichloromethane:toluene.

22.4 g of a violet solid were obtained, which corresponds to a yield of 74%.

25 Analytical data:

^1H NMR (500MHz, CH_2Cl_2 , 25°C): δ = 8.59-8.56 (m, 2H); 8.46-8.38 (m, 4H); 8.21-8.19 (d, 1H); 7.69-7.60 (m, 6H); 7.52-7.25 (m, 17H); 2.79-2.77 (m, 2H); 1.44 (s, 12H); 1.17-1.15 (d, 12H)

30

Step c:

22.4 g (23 mmol) of step b and 73 g (1.3 mol) of KOH were introduced into 200 ml of 2-methyl-2-butanol and the mixture was stirred at reflux for 17 h.

35

After cooling, the reaction mixture was added to 1 l of ice-water + 50 ml of concentrated acetic acid. The orange-brown solid was filtered through a frit and washed with water.

The solid was dissolved in dichloromethane and extracted with demineralized water. 10 ml of concentrated acetic acid were added to the organic phase, which was stirred at RT. The solvent was removed from the solution. The residue was extracted by stirring with methanol at RT for 30 min, filtered with suction through a frit and dried at 55°C in a 5 vacuum drying cabinet.

This afforded 17.5 g of a violet solid, which corresponds to a yield of 94%. The product was used unpurified in the next step.

10 *Step d:*

17.5 g (22 mmol) of stage c, 16.4 g (220 mmol) of glycine and 4 g (22 mmol) of zinc acetate were introduced into 350 ml of N-methylpyrrolidone and the mixture was stirred at 130°C for 12 h.

15 After cooling, the reaction mixture was added to 1 l of demineralized water. The precipitate was filtered through a frit, washed with water and dried at 70°C in a vacuum drying cabinet.

20 Purification was effected by means of column chromatography with the eluent 3:1 dichloromethane:ethanol + 2% triethylamine. The isolated product was extracted by stirring at 60°C with 50% acetic acid. The solid was filtered off with suction through a frit, washed with water and dried at 80°C in a vacuum drying cabinet.

25 7.9 g of a violet solid were obtained, which corresponds to a yield of 42%.

Analytical data:

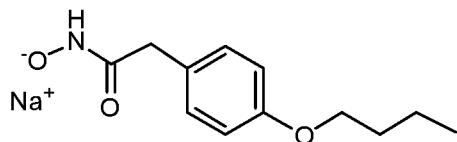
30 ^1H NMR (500MHz, THF, 25°C): δ = 8.37-8.34 (m, 2H); 8.25-8.18 (m, 4H); 8.12-8.10 (d, 1H); 7.74-7.70 (m, 4H); 7.59-7.53 (m, 4H); 7.45-7.43 (m, 4H); 7.39-7.37 (m, 2H); 7.32-7.22 (m, 6H); 4.82 (s, 2H); 1.46 (s, 12H)

(H) Synthesis of compounds ID662:

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12 Jan 2016

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ID662

ID662 was prepared by reacting the corresponding commercially available hydroxamic acid [2-(4-butoxyphenyl)-N-hydroxyacetamide] with sodium hydroxide.

5 In the claims which follow and in the preceding description of the invention, except where the context requires otherwise due to express language or necessary implication, the word " comprise" or variations such as " comprises" or " comprising" is used in an inclusive sense, i.e. to specify the presence of the stated features but not to preclude the presence or addition of further features in various embodiments of the invention.

0 It is to be understood that, if any prior art publication is referred to herein, such reference does not constitute an admission that the publication forms a part of the common general knowledge in the art, in Australia or any other country.

5

List of reference numerals

110	Photovoltaic element
112	Dye solar cell
5 114	Substrate
116	First electrode
118	Blocking layer
120	n-semiconductive material
122	Dye
10 124	Carrier element
126	p-semiconductor
128	Matrix material
130	Silver in oxidized form
132	Second electrode
15 134	Layer structure
136	Encapsulation
138	Fermi level
140	HOMO
142	LUMO
20 144	Characteristic for comparative sample without silver in oxidized form, t = 0
146	Characteristic for comparative sample without silver in oxidized form, t = 2 days
148	Characteristic for example 1 sample, t = 0
150	Characteristic for example 1 sample, t = 2 days
25	

Claims

1. A photovoltaic element for conversion of electromagnetic radiation to electrical energy, wherein the photovoltaic element comprises at least one first electrode, at least one n-semiconductive metal oxide, at least one electromagnetic radiation-absorbing dye, at least one solid organic p-semiconductor and at least one second electrode, wherein the p-semiconductor comprises silver in oxidized form.
2. The photovoltaic element according to claim 1, wherein the p-semiconductor is producible or has been produced by applying at least one p-conductive organic material and silver in oxidized form to at least one carrier element.
3. The photovoltaic element according to claim 2, wherein silver is applied in the form of at least one silver(I) salt $[Ag^+]_m[A^{m-}]$ where $[A^{m-}]$ is an anion of an organic or inorganic acid and m is an integer in the range from 1 to 3.
4. The photovoltaic element according to claim 3, wherein $[A^{m-}]$ has a structure of the formula (II)



where R^a is a fluorine group -F or an alkyl radical, cycloalkyl radical, aryl radical or heteroaryl radical each substituted by at least one fluorine group or cyano group,

and where X is - O- or - N-R^b,

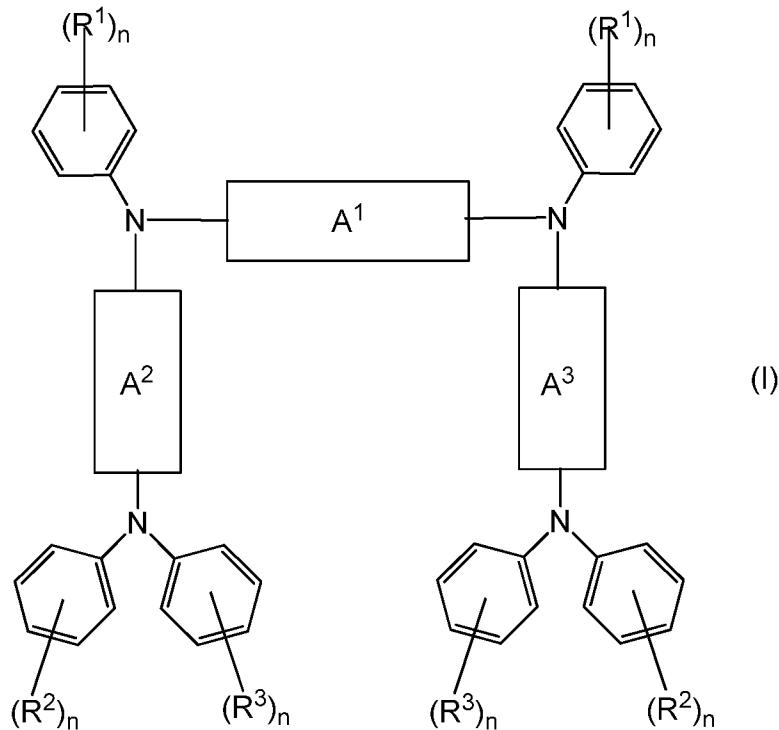
and where R^b comprises a fluorine group - F or a cyano group,

and where R^b further comprises a group of the formula - S(O)₂-.

5. The photovoltaic element according to claim 4, wherein R^a is selected from the group consisting of - F, -CF₃, -CF₂-CF₃ and - CH₂-CN.
6. The photovoltaic element according to claim 4 or 5, where X is - N-R^b, and where R^b is selected from the group consisting of - S(O)₂- F, -S(O)₂-CF₃, - S(O)₂-CF₂-CF₃ and - S(O)₂- CH₂-CN.
7. The photovoltaic element according to any one of claims 3 to 5, wherein $[A^{m-}]$ is selected from the group consisting of bis(trifluoromethylsulfonyl)imide (TFSI-),

bis(trifluoroethylsulfonyl)imide, bis(fluorosulfonyl)imide and trifluoromethylsulfonate.

8. The photovoltaic element according to claim 3, wherein $[A^{m-}]$ is a trifluoroacetate group.
9. The photovoltaic element according to claim 3, wherein $[A^{m-}]$ is NO_3^- .
10. The photovoltaic element according to any one of claims 3 to 8, wherein the p-semiconductor is producible or has been produced by applying at least one p-conductive organic material and at least one silver(I) salt $[Ag^+]_m[A^{m-}]$ to at least one carrier element, the application being effected by deposition from a liquid phase comprising the at least one p-conductive organic material and the at least one silver(I) salt $[Ag^+]_m[A^{m-}]$.
11. The photovoltaic element according to claim 10, wherein the liquid phase further comprises at least one solvent.
12. The photovoltaic element according to claim 11, wherein Ag^+ is in essentially homogeneous distribution in the p-conductive organic material.
13. The photovoltaic element according to either one of the claims 11 or 12, wherein the p-conductive organic material comprises at least one low molecular weight organic p-semiconductor.
14. The photovoltaic element according to any one of claims 2 to 11, wherein the p-conductive organic material comprises a spiro compound, and/or a compound with the structural formula:



in which

5 A^1, A^2, A^3 are each independently optionally substituted aryl groups or heteroaryl groups,

0 R^1, R^2, R^3 are each independently selected from the group consisting of the substituents $-R$, $-OR$, $-NR_2$, $-A^4-OR$ and $-A^4-NR_2$,

15 where R is selected from the group consisting of alkyl, aryl and heteroaryl,

and

15 where A^4 is an aryl group or heteroaryl group, and

where n at each instance in formula I is independently a value of 0, 1, 2 or 3,

20 with the proviso that the sum of the individual n values is at least 2 and at least two of the R^1, R^2 and R^3 radicals are $-OR$ and/or $-NR_2$.

15. The photovoltaic element according to any one of the preceding claims, further comprising at least one encapsulation, wherein the encapsulation is designed to shield the photovoltaic element, from a surrounding atmosphere.

16. The photovoltaic element according to either one of claims 10 or 11, wherein the liquid phase comprises the at least one silver(I) salt $[Ag^+]_m[A^m^-]$ in a concentration of 0.5 mM/ml to 50 mM/ml.
17. A process for producing a solid organic p-semiconductor for use in an organic component, especially a photovoltaic element according to any one of the preceding claims, wherein at least one p-conductive organic matrix material and at least silver in oxidized form are applied to at least one carrier element from at least one liquid phase.
18. The process according to claim 17, wherein the liquid phase further comprises at least one solvent.
19. The process according to either one of claims 17 or 18, wherein the process is performed at least partly in a low-oxygen atmosphere.
20. A process for producing a photovoltaic element, wherein, in the process, at least one first electrode, at least one n-semiconductive metal oxide, at least one electromagnetic radiation-absorbing dye, at least one solid organic p-semiconductor and at least one second electrode are provided, wherein the p-semiconductor is produced by a process according to any one of claims 17 to 19.

FIG.1

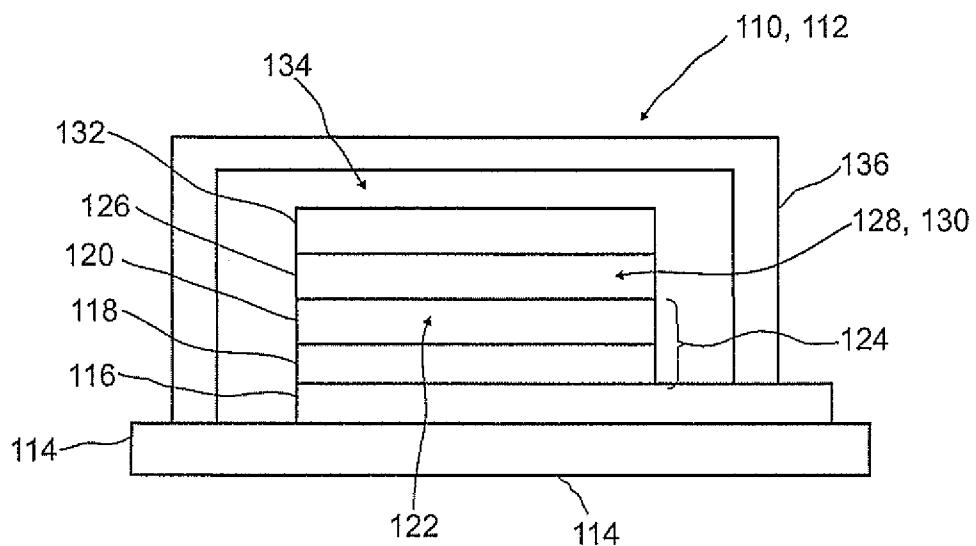


FIG.2

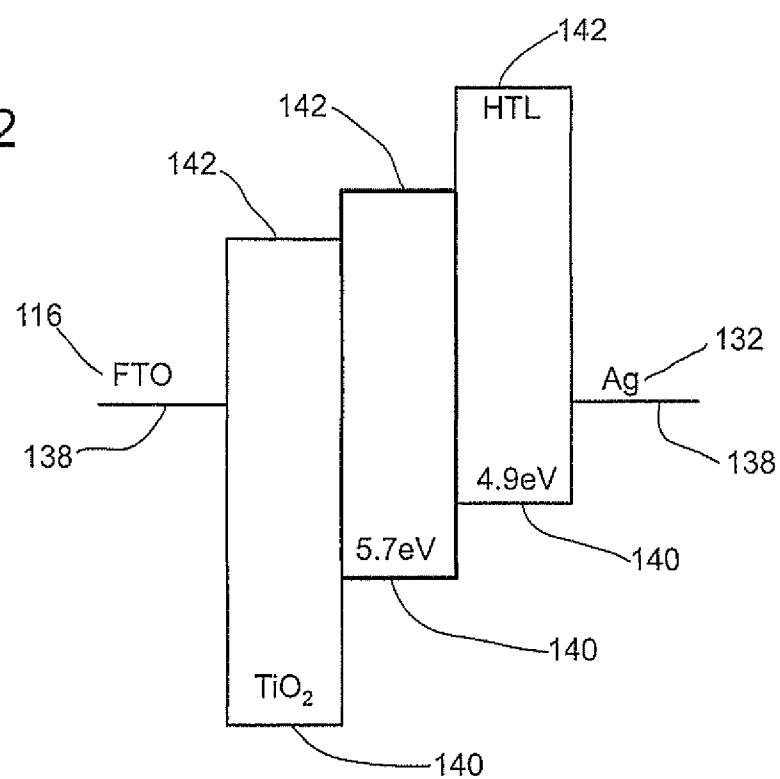


FIG.3

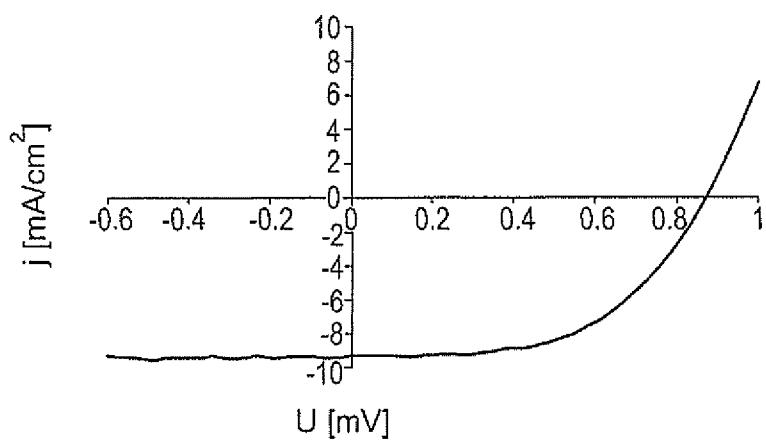


FIG.4

